

Overview of Scanning microwave microscopy (SMM)

- Calibration
- Applications (semicon, materials, bio)
- Advanced solutions



7500 SMM

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Agenda

- Overview & SMM Introduction
- Dopant profiling (dC/dV) for semiconductors
- Complex impedance for materials science
 - Calibration
 - Subsurface imaging
 - Resistivity from resistance
 - Dielectric quantification
 - 2D materials (graphene)
- Multi-modal SMM solutions
 - Augmented SMM (SMM plus add-ons)
 - New modes: transmission, magnetic, and QuBits
- Bio-SMM & liquid imaging
- Summary

Collaborators & Acknowledgments (selected)

Univ. Linz, Austria

Biophysics Institute: *Georg Gramse, Silviu Tuca*, Peter Hinterdorfer

Keysight Austria

Enrico Brinciotti, Manuel Kasper, Giorgio Badino, Manuel Moertelmaier, Ivan Alic

Keysight Europe & USA

Matthias Fenner, Hassan Tanbakuchi
Shijie Wu, Dirk Orgassa, Matt Richter
Michael Dieudonne

TU Vienna, Austria

Juergen Smoliner

METAS (Bern)

Johannes Hoffmann

NIST USA

Pavel Kabos

IBEC Barcelona

Gabriel Gomila

CNR-IMM

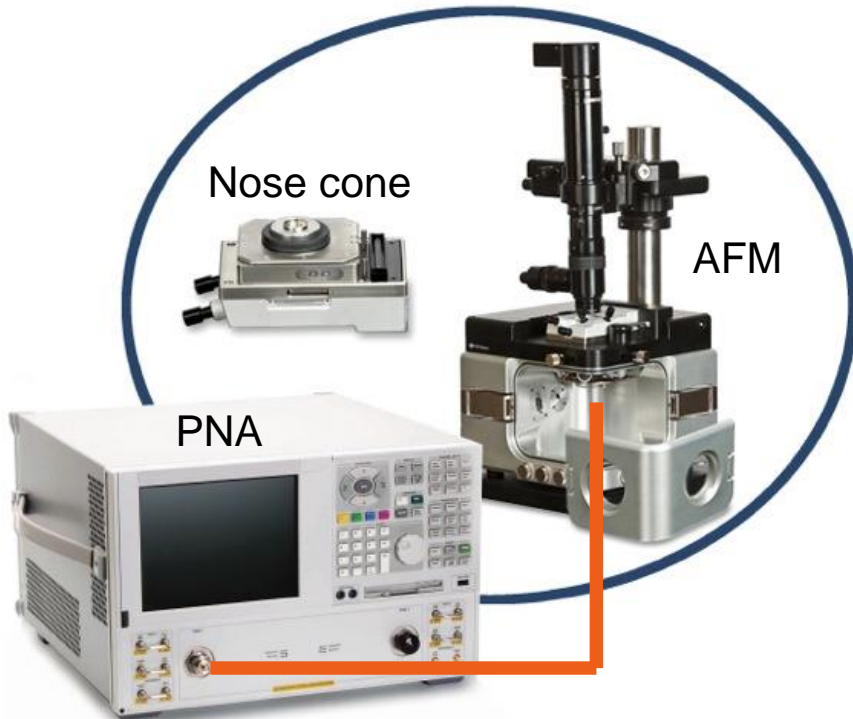
Romollo Marcelli

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What is SMM?

SMM = PNA + AFM



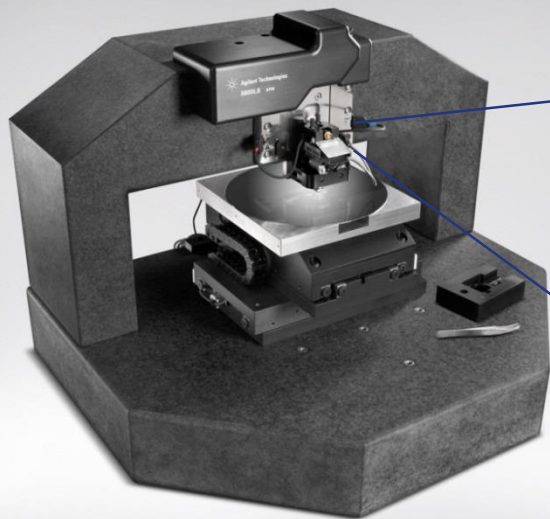
- SMM: Atomic force microscope (AFM) interfaced with a Performance Network Analyzer (PNA)
- PNA Network analysis for microwave frequencies (1-20 GHz)
- PNA: stimulus-response instrument, Measuring magnitude and phase characteristics of a sample

Consider:

- High Frequency allows to measure also non-conductive samples (eg DC STM only on conductive samples)
- GHz Frequency results in better sensitivity (eg compared to MHz impedance AFM)
- Microwaves have good sample penetration capabilities

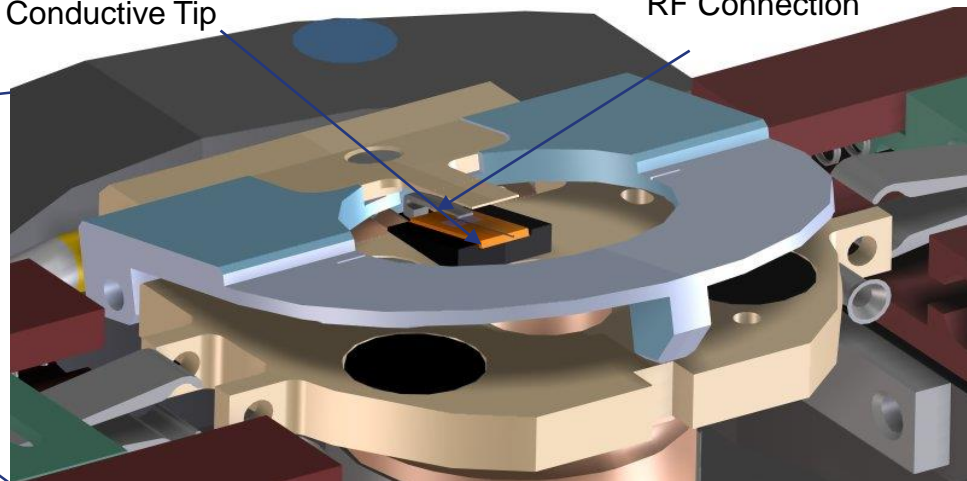
The Scanning Microwave Microscope

5600LS AFM



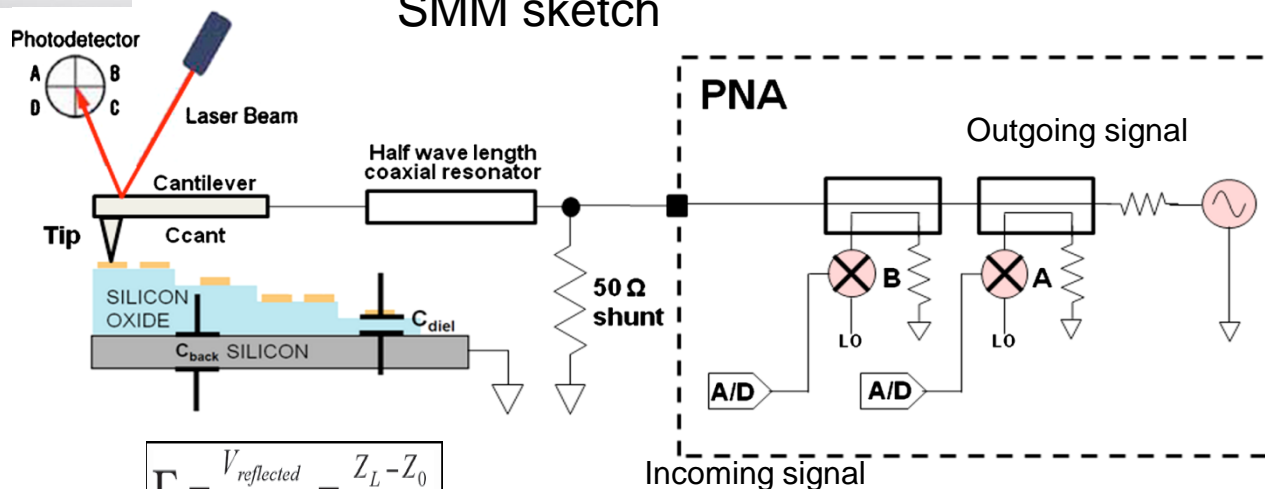
Conductive Tip

RF Connection



PNA

SMM sketch

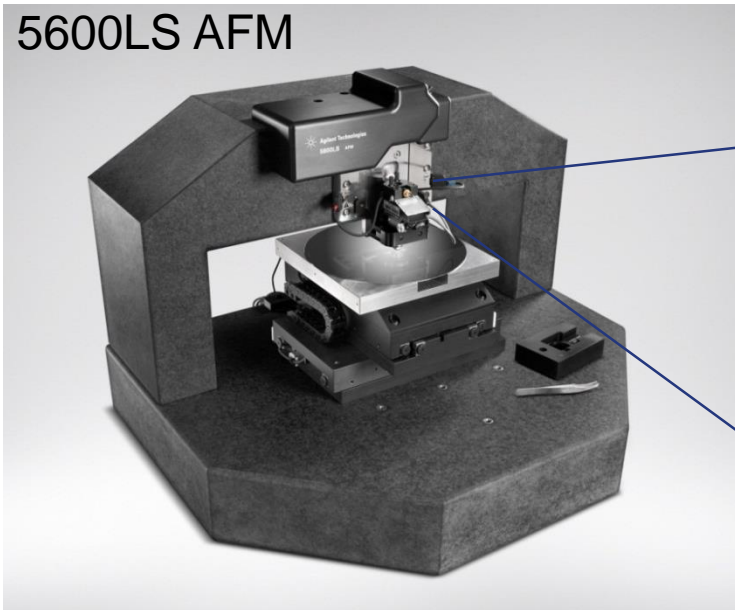


Huber et al., RSI, 81, 2010, 113701

$$\Gamma = \frac{V_{\text{reflected}}}{V_{\text{incident}}} = \frac{Z_L - Z_0}{Z_L + Z_0}$$

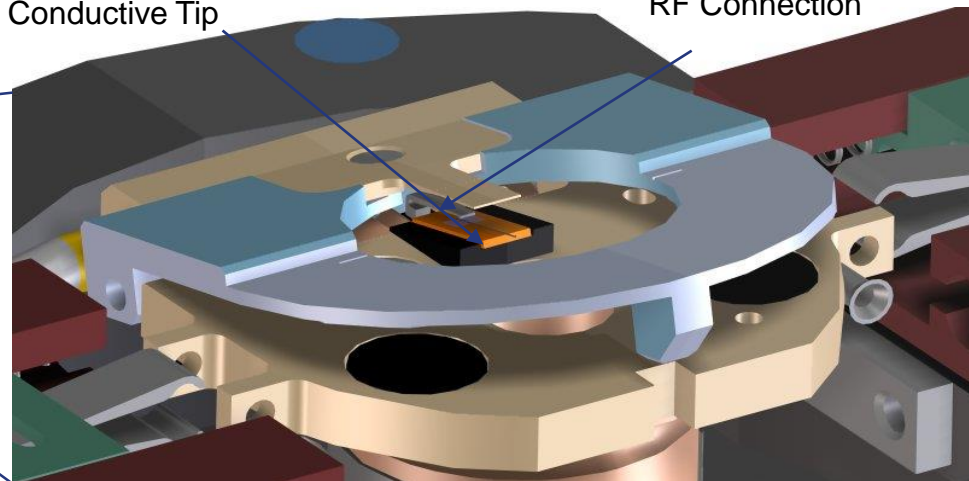
The Scanning Microwave Microscope

5600LS AFM



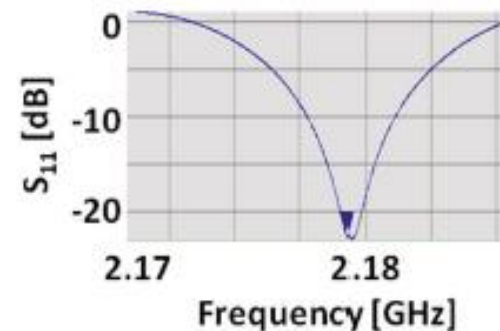
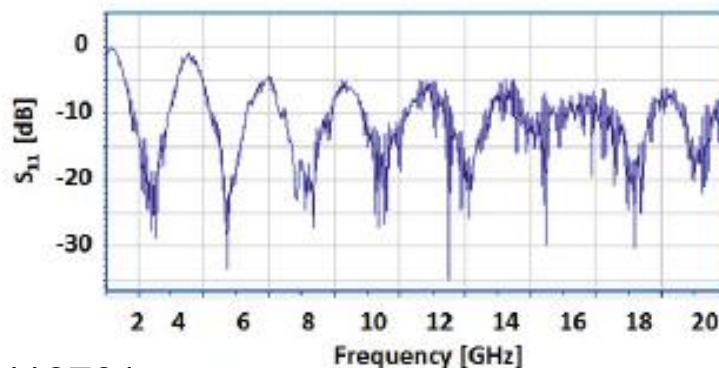
Conductive Tip

RF Connection



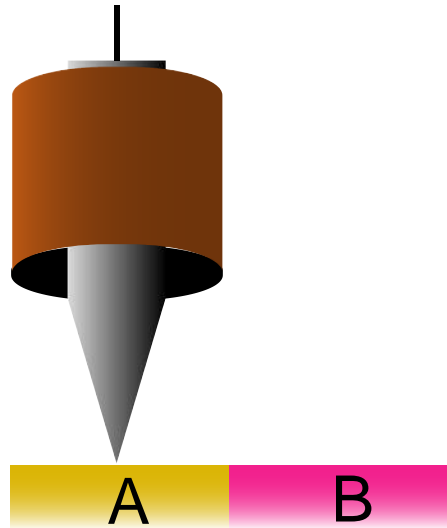
PNA

Resonance matches at multiple frequencies



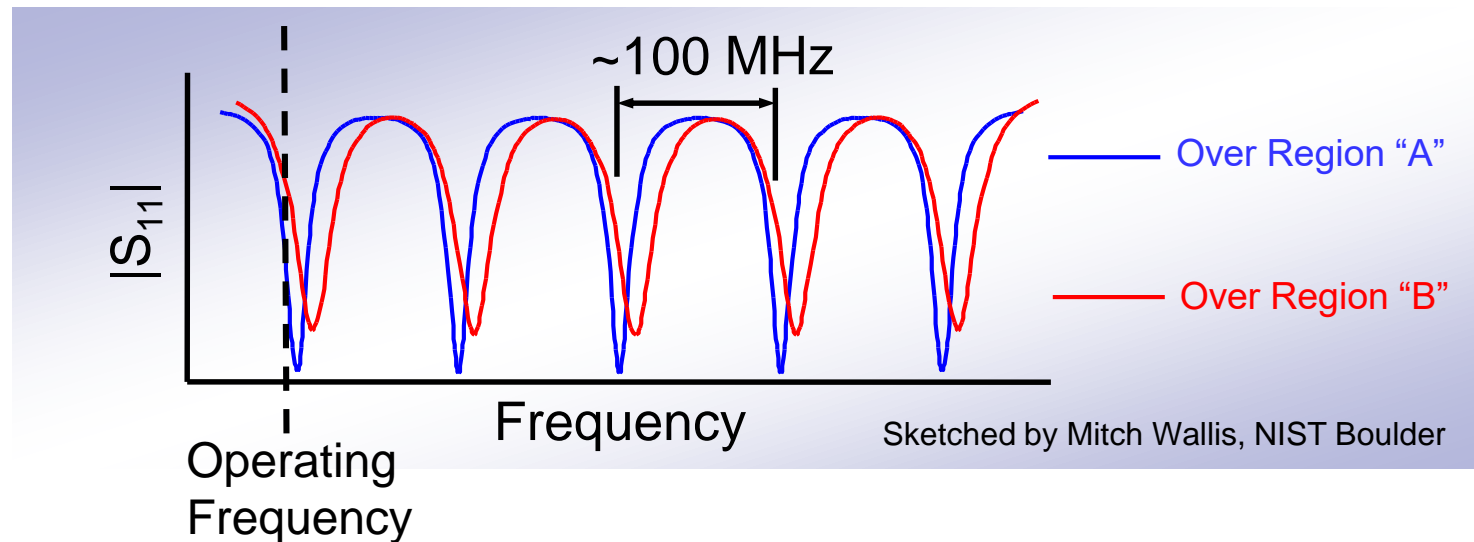
Huber et al., RSI, 81, 2010, 113701

SMM Contrast Mechanism: also on non-conductive samples

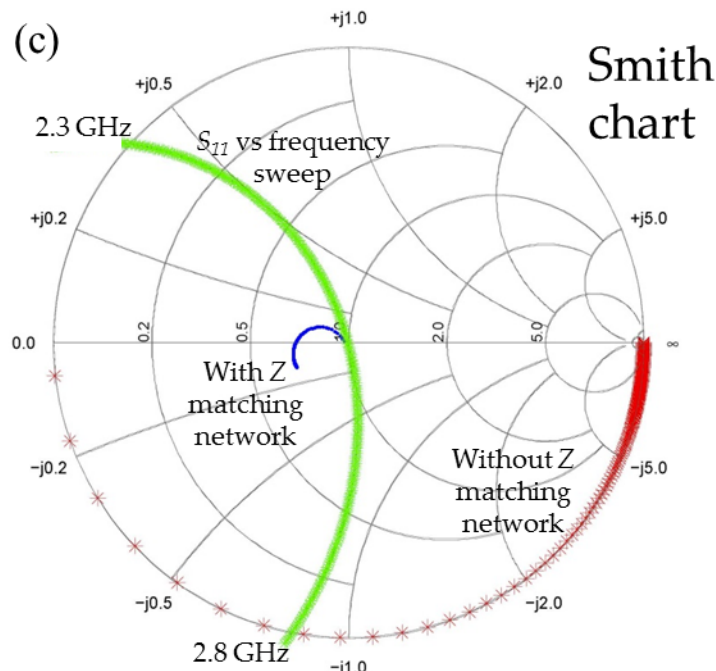
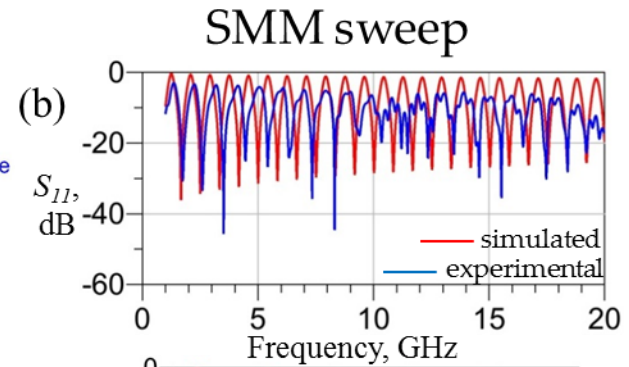
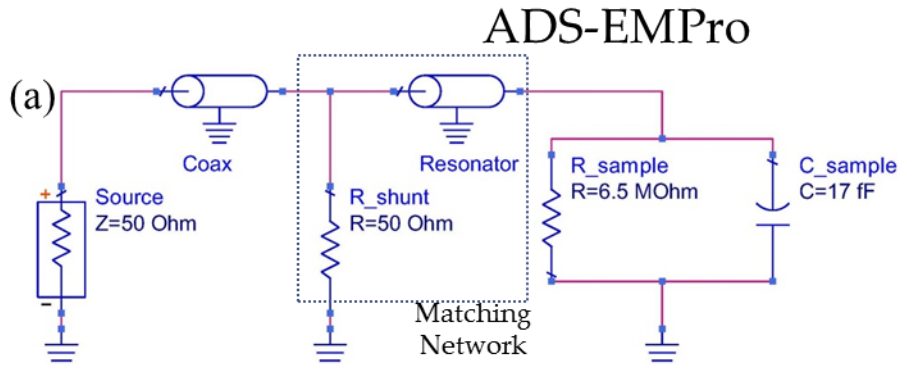


Regions “A” and “B” present different impedances and material properties of the two regions. Examples:

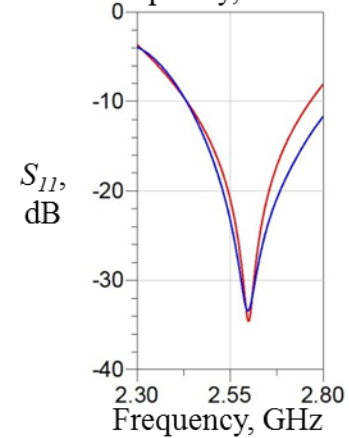
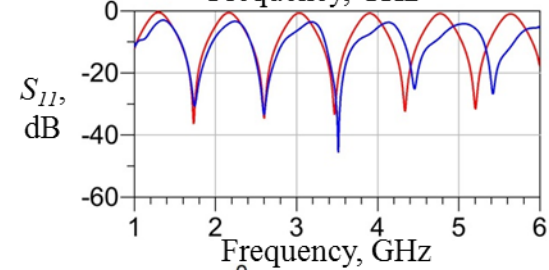
- complex permittivity ($\epsilon' + i \epsilon''$)
- complex permeability ($\mu' + i \mu''$) & magnetic prop.
- conductivity (σ)
- carrier concentration / dopant (n)



ADS model and Smith Chart analysis



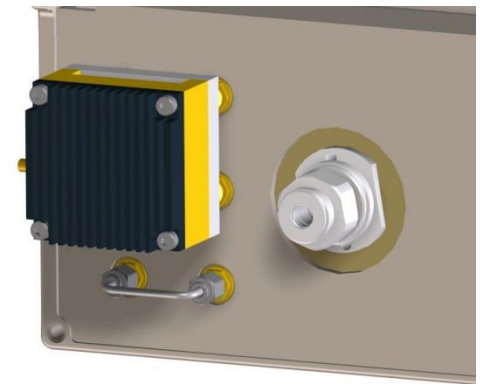
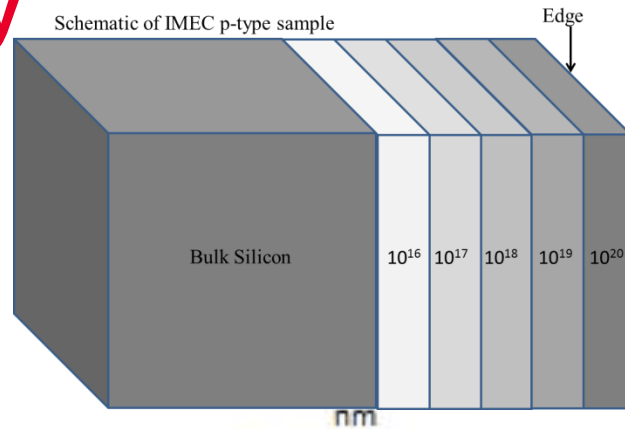
Smith chart on the PNA window



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Dopant density



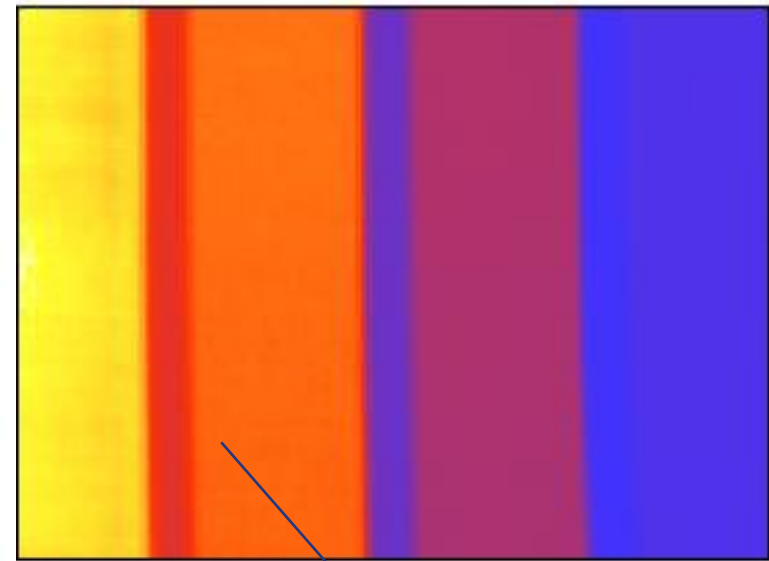
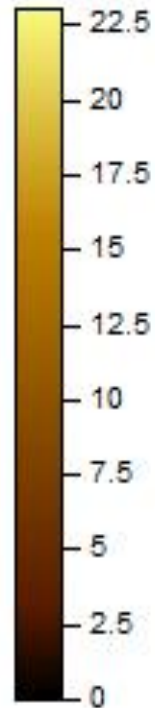
bulk

Topography

edge

dC/dV Amplitude

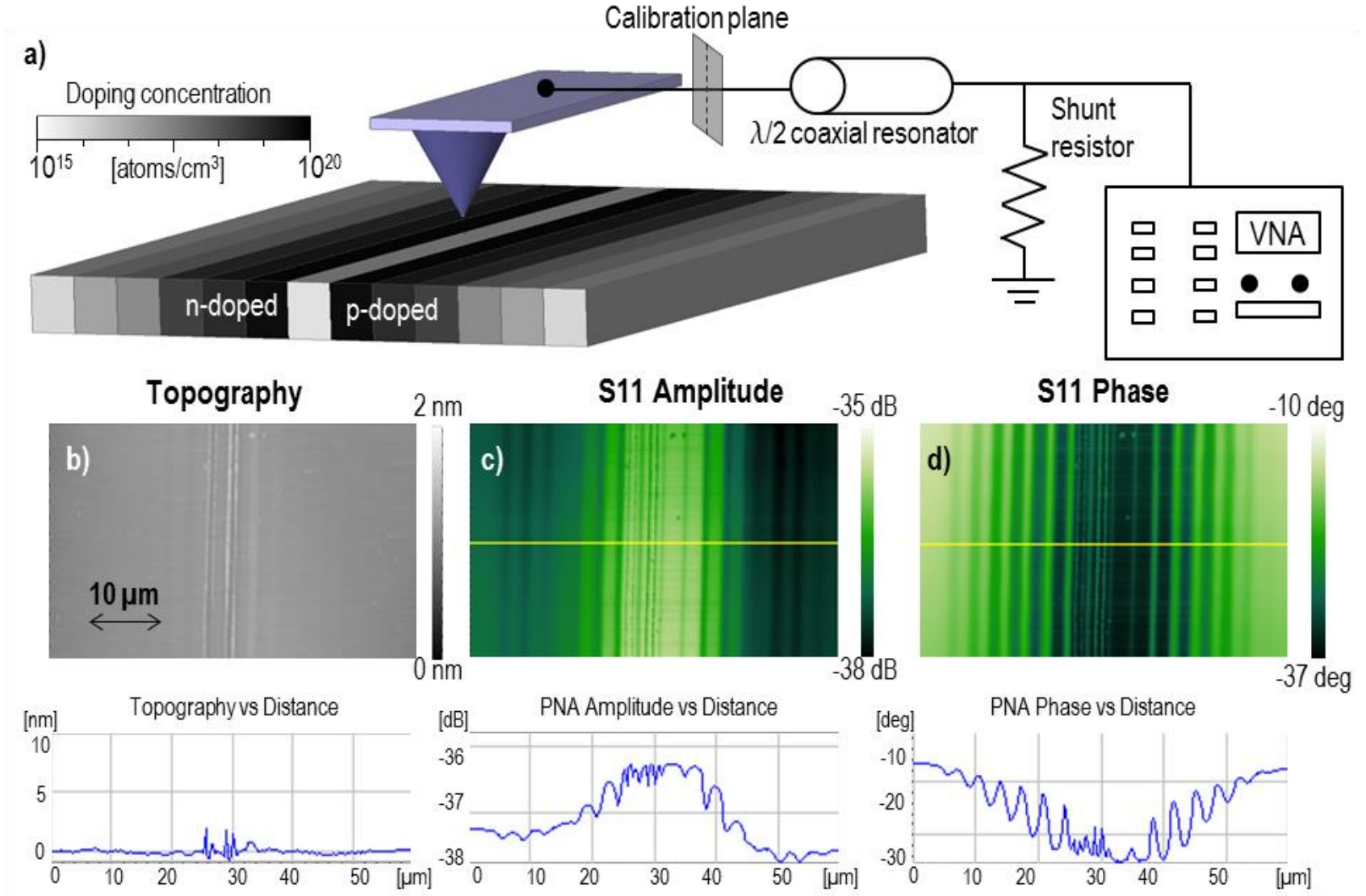
V



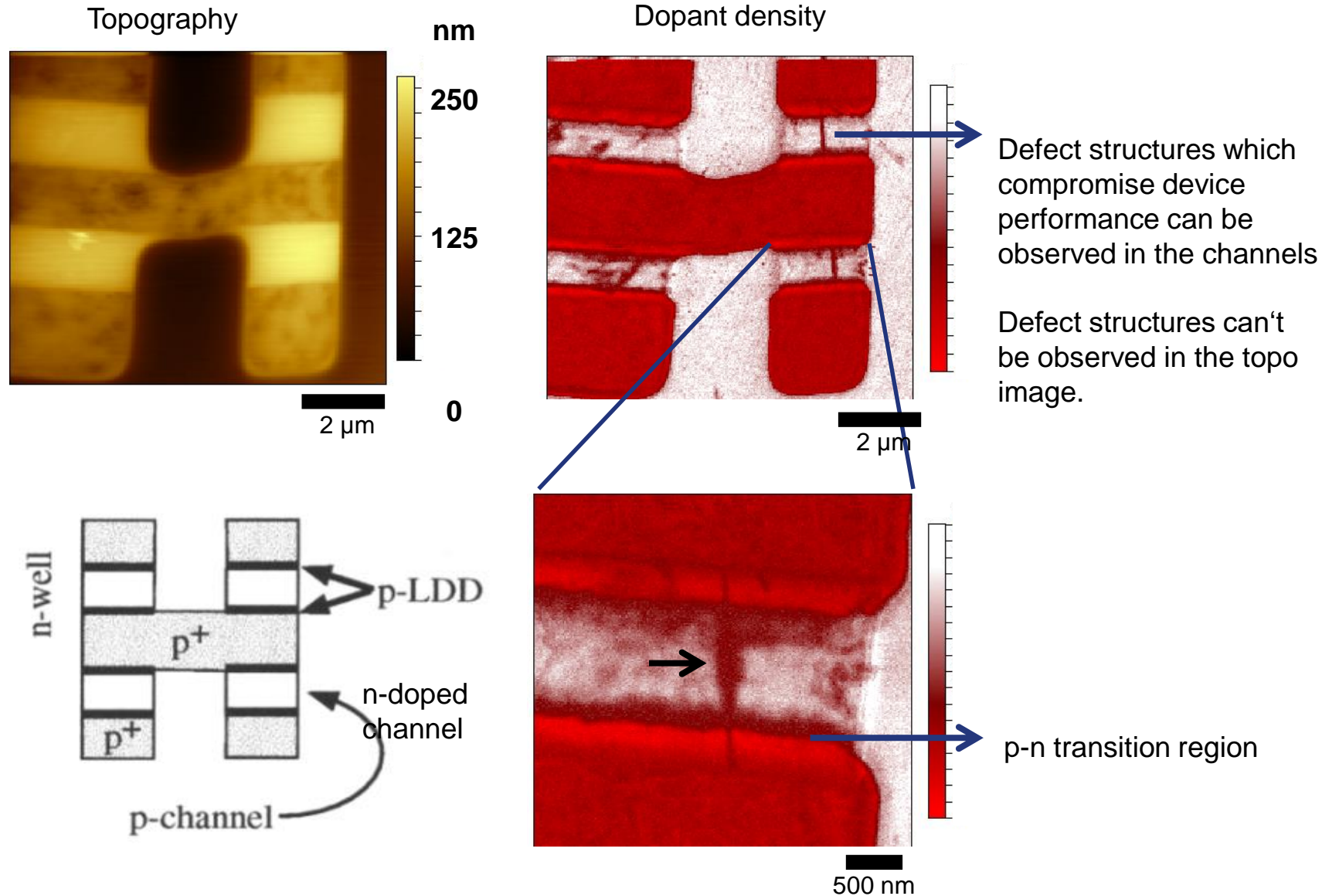
Different dopant densities

J. Appl. Physics 111, 014301, 2012

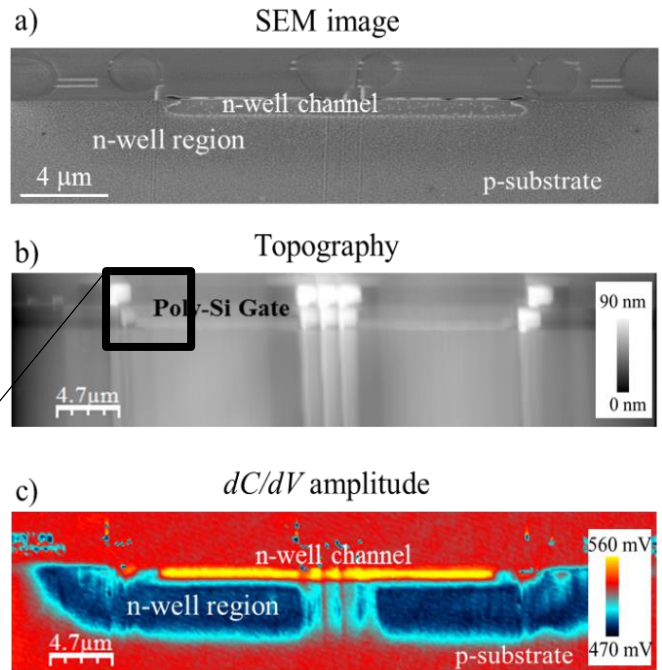
Dopant profiling on the nano-scale with a new calibration sample



Dopant profiling application to SRAM

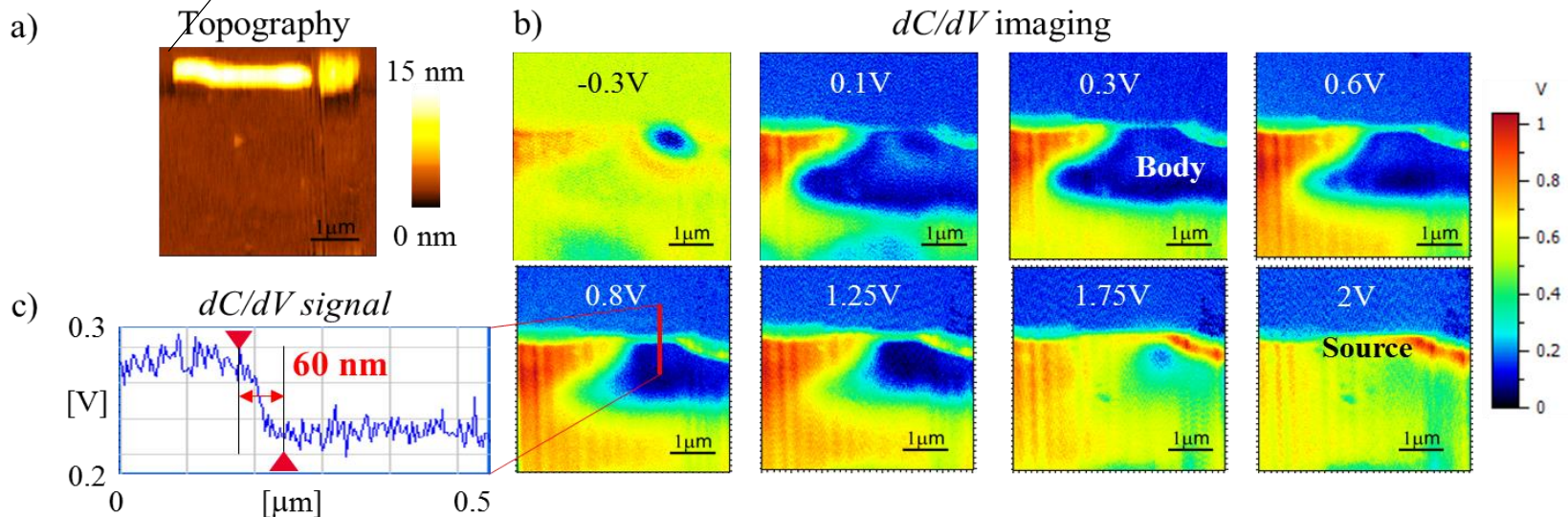


High voltage lateral diffused MOS transistor LDMOS

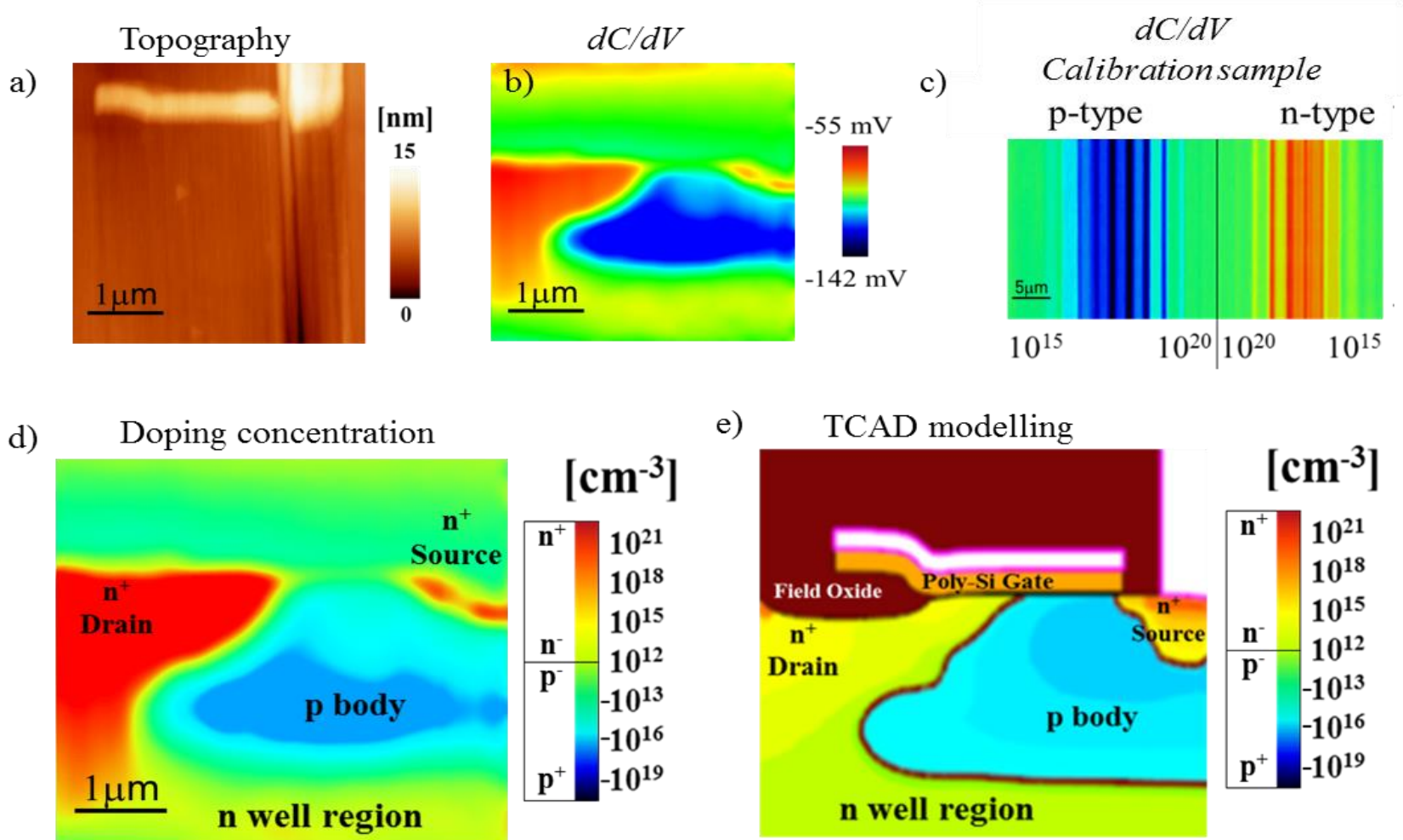


*Brinciotti et al., submitted
Aug 2016,
Keysight Labs, AMS
Austria, TU Vienna*

4 μm x 4 μm area including poly-silicon gate, field oxide, p-body, n^+ -source, and n^+ -drain.



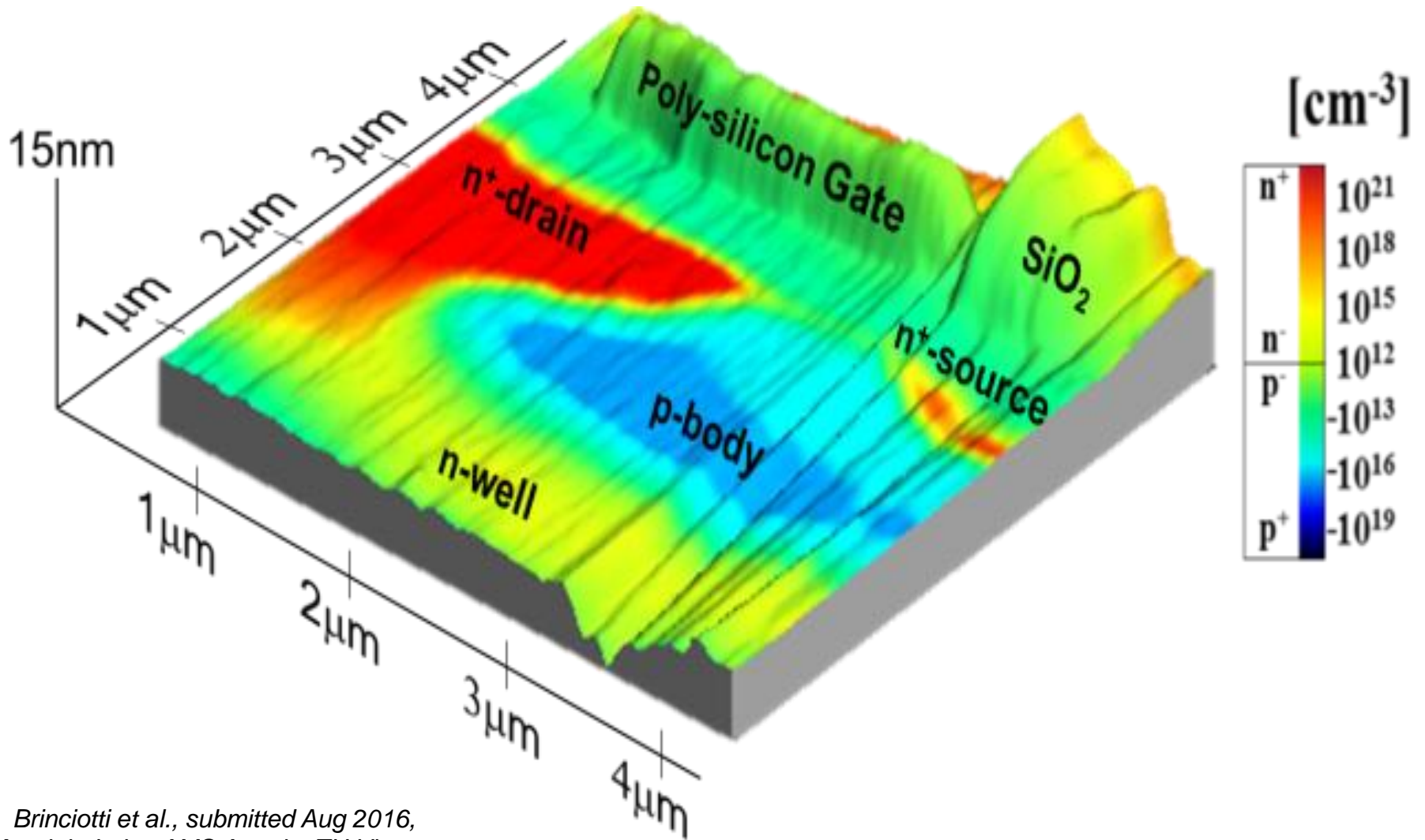
High voltage lateral diffused MOS transistor LDMOS



Brinciotti et al., submitted Aug 2016,
 Keysight Labs, AMS Austria, TU Vienna

Quantitative dopant calibration

High voltage lateral diffused MOS transistor LDMOS



Brinciotti et al., submitted Aug 2016,
Keysight Labs, AMS Austria, TU Vienna

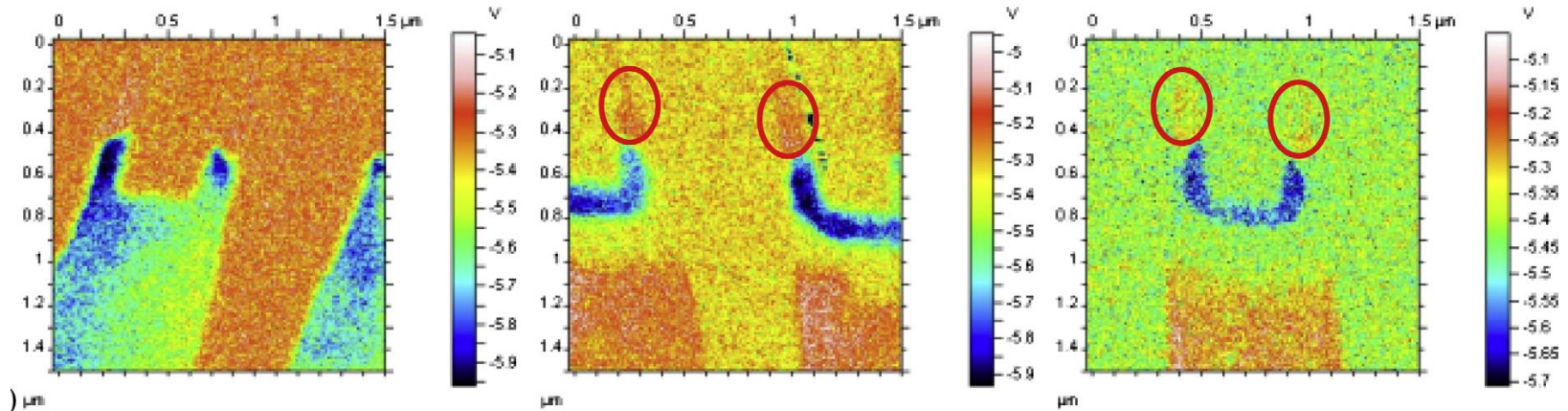
Quantitative dopant calibration

Dopant profiling on the nano-scale

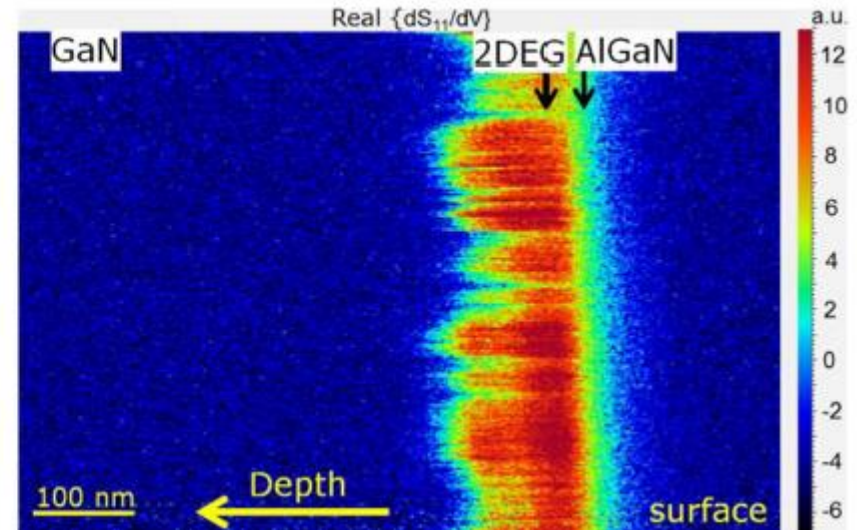
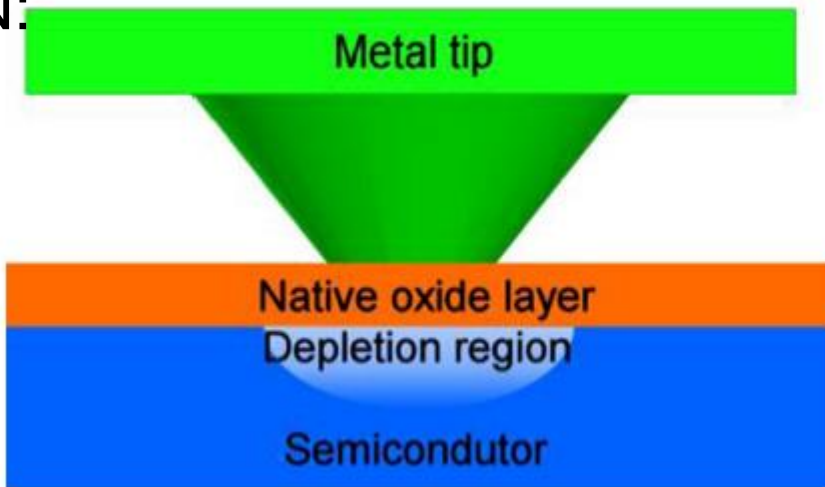
Silicon:

Nanoscale DMOS measurements

DC tip bias



GaN:



T. Schweinboeck and S. Hommel (Infineon Munich)
Microelectronic Reliability 2014, 54, 2070-4 (upper part)
Microelectronic Reliability 2016 (lower part)

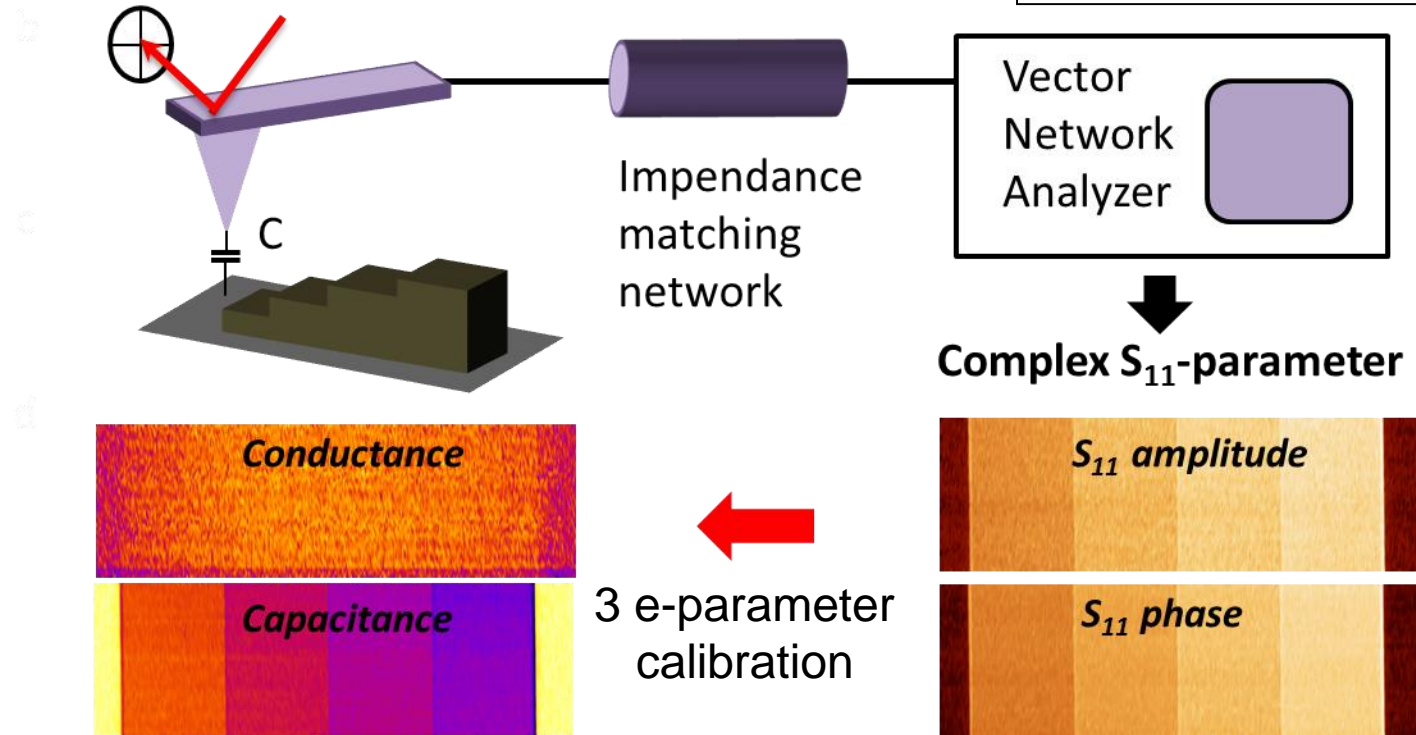
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Complex impedance calibration: new method

Workflow and calibration

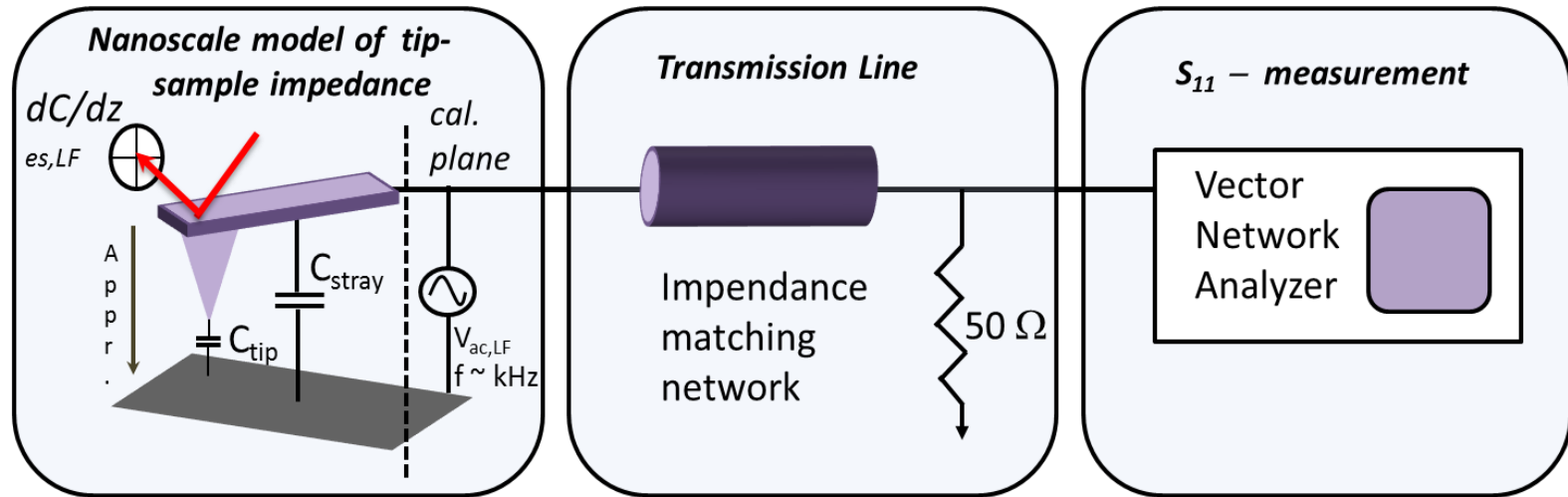
$$S_{11} = \frac{Z_{tip} - Z_{ref}}{Z_{tip} + Z_{ref}}$$
$$S_{11m} = e_{00} + \frac{S_{11}e_{01}}{1 - e_{11}S_{11}}$$



-> NO calibration sample required

(therefore no stray capacitance issues, only for non-lossy samples like semiconductors, dielectrics and oxides; not for water)

Complex impedance calibration: new method



Z_{in} from dC/dz_{LF} -EFM curve

Blackbox Calibration

Complex S_{11} -parameter

$$S_{11,a} = \frac{Z_{in} - Z_{ref}}{Z_{in} + Z_{ref}}$$

$$S_{11,m} = e_{00} + e_{01} \frac{S_{11,a}}{1 - e_{11} S_{11,a}}$$

$$S_{11,m}$$

Tip-substrate
capacitance model

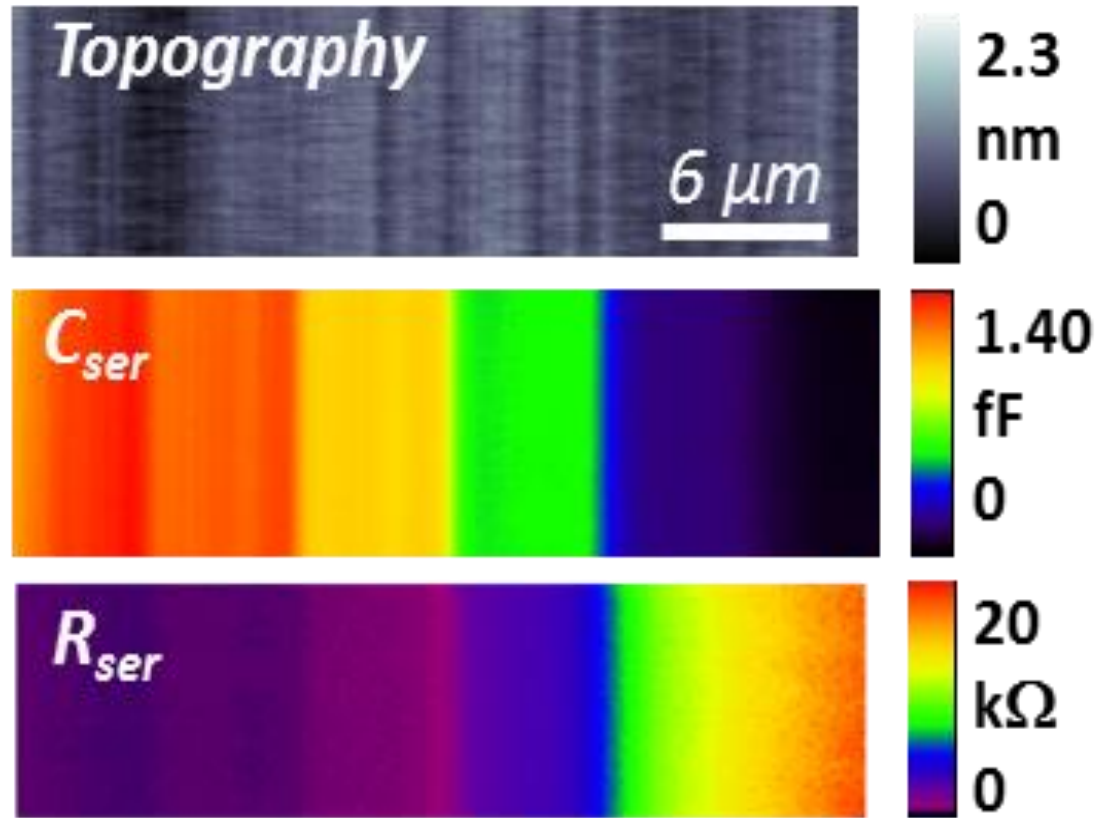
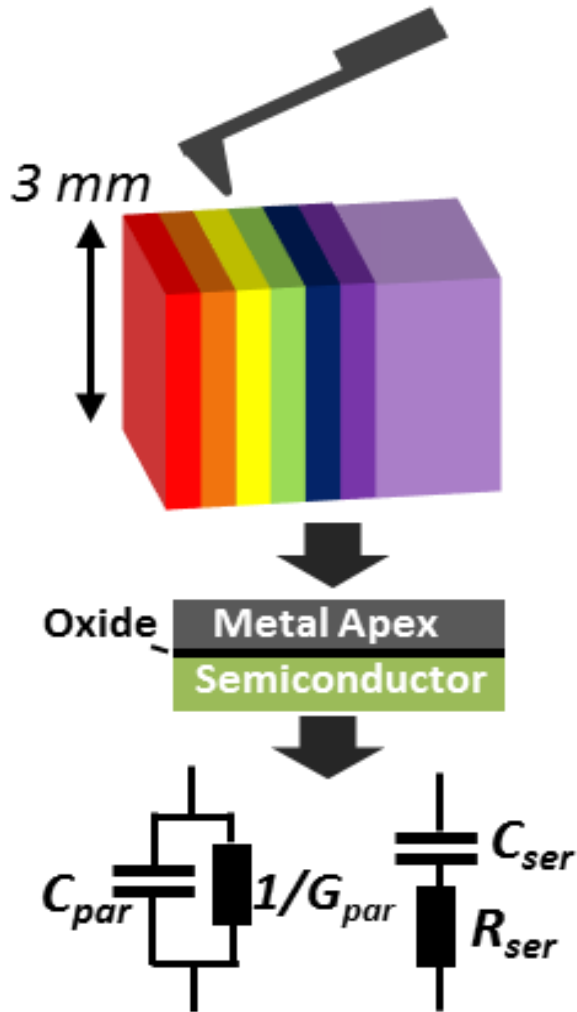
e_{00}, e_{01}, e_{11}

Calibrated
Impedance
Image/ Curve

Tip geometry Calibration + Blackbox Calibration parameters

Gramse et al., Nanotechnology 25 (2014)

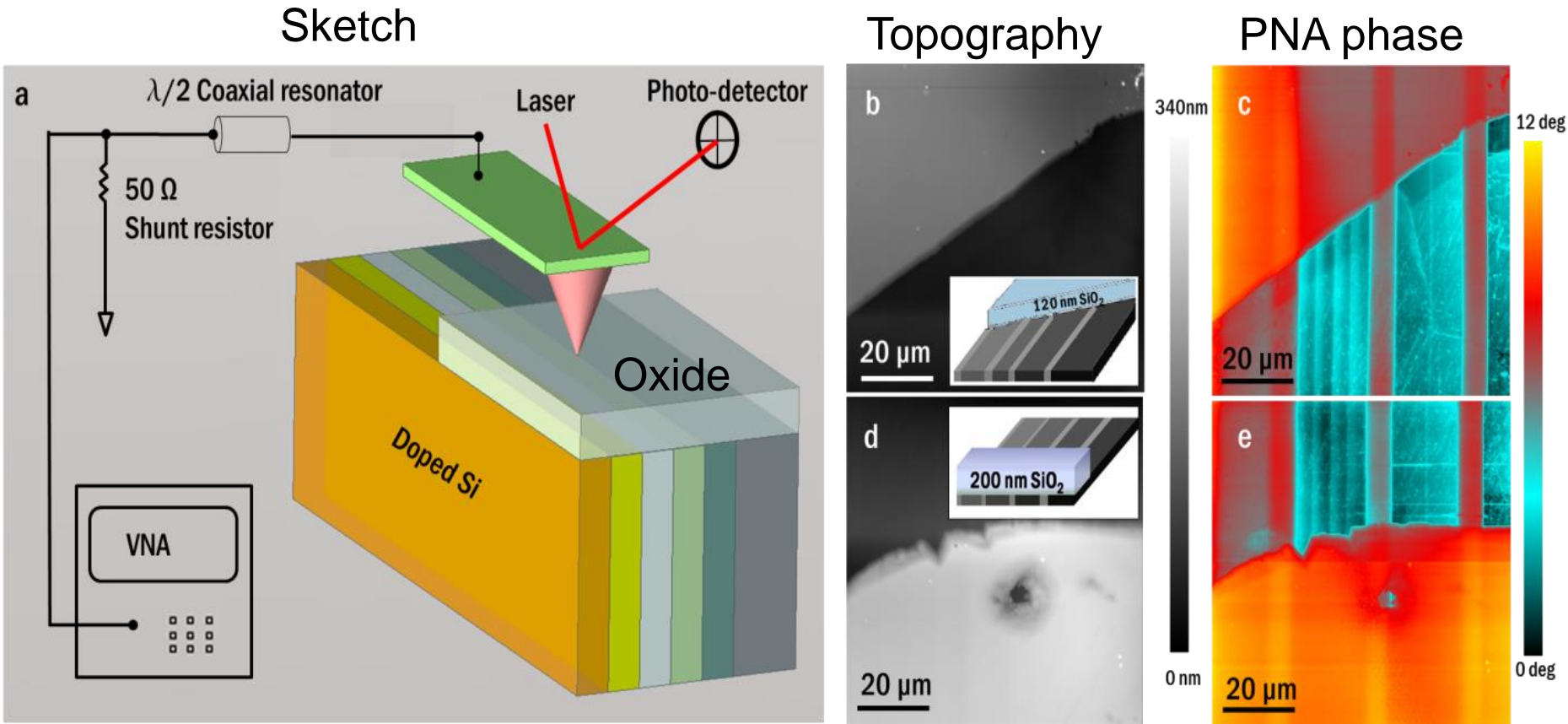
Application I: Complex impedance of doped silicon



-> resistance of doped silicon

Gramse et al., Nanotechnology 25 (2014)

Application II: complex impedance & subsurface imaging

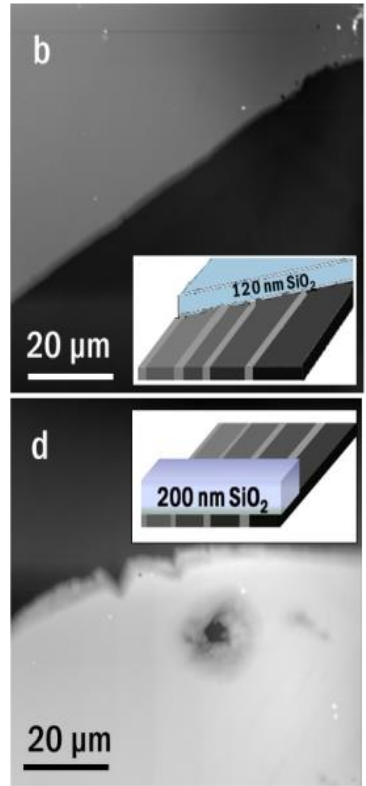


Application II: complex impedance & subsurface imaging

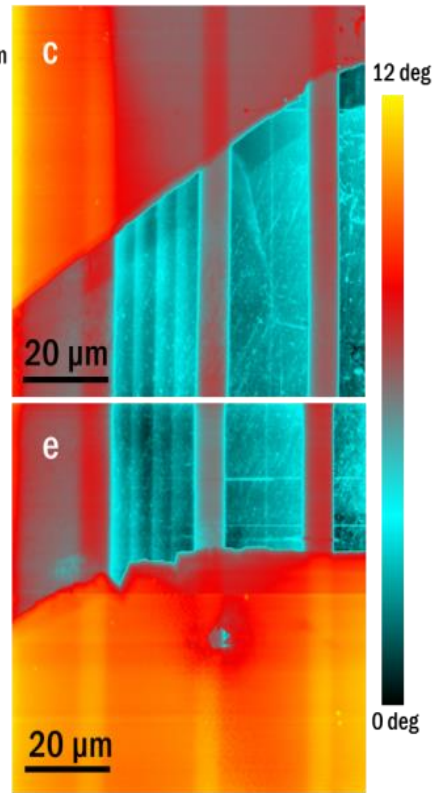
Cover story April 2015



Topography

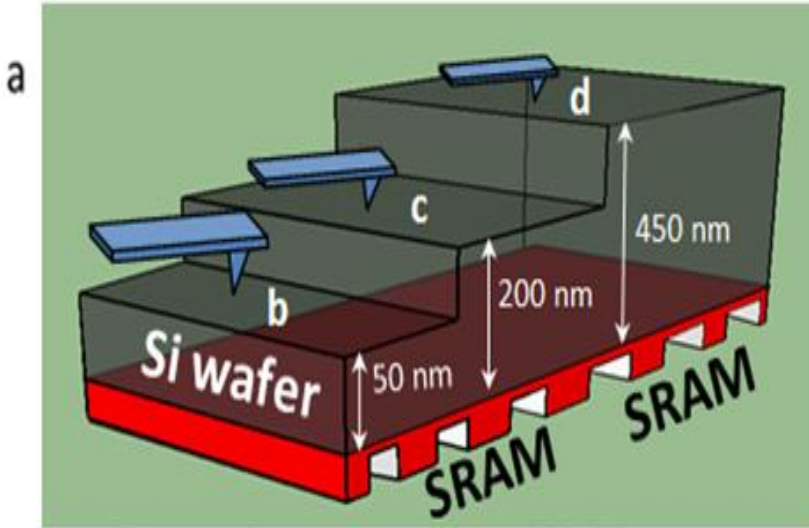


PNA phase

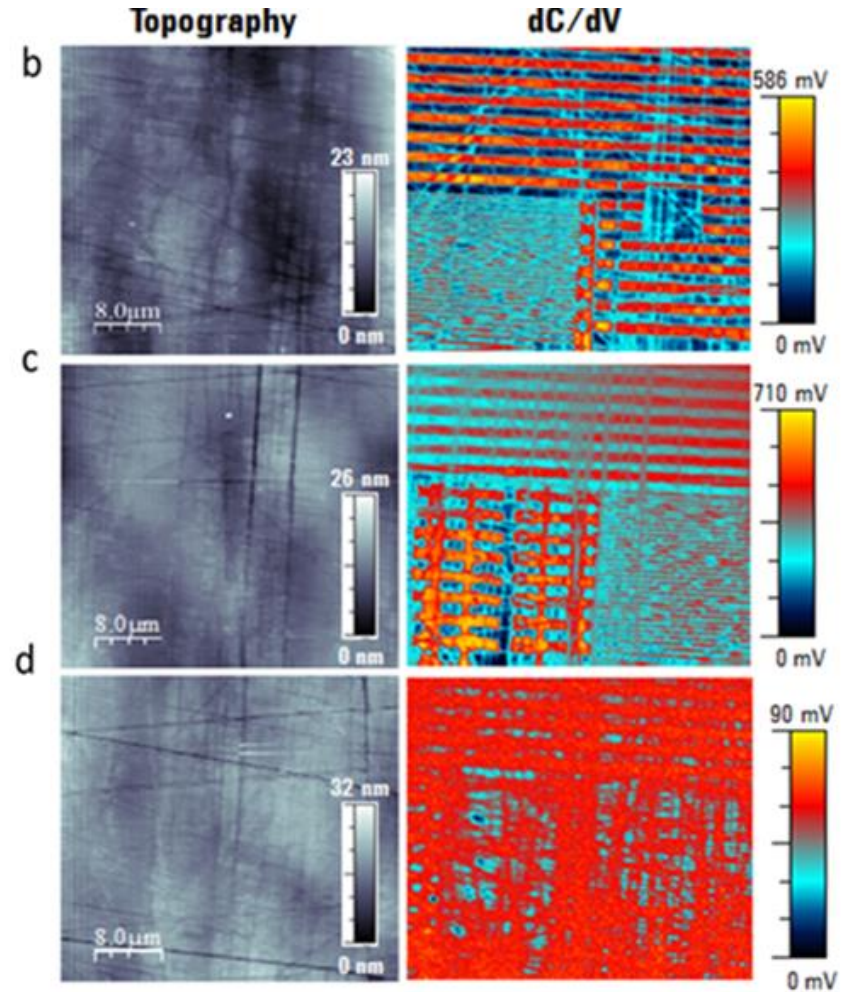


Gramse & Brinciotti et al., Nanotechnology (26) 2015, 35701 (9 pages). Cover

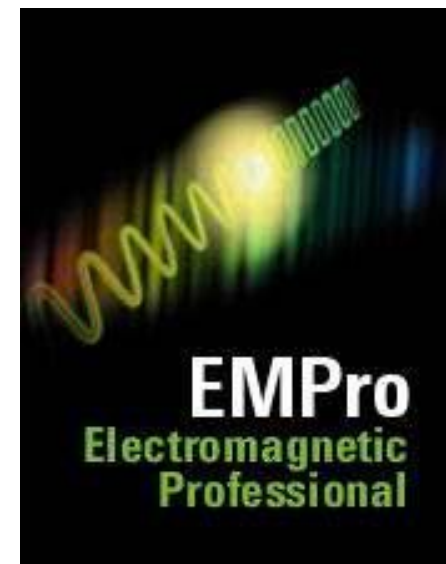
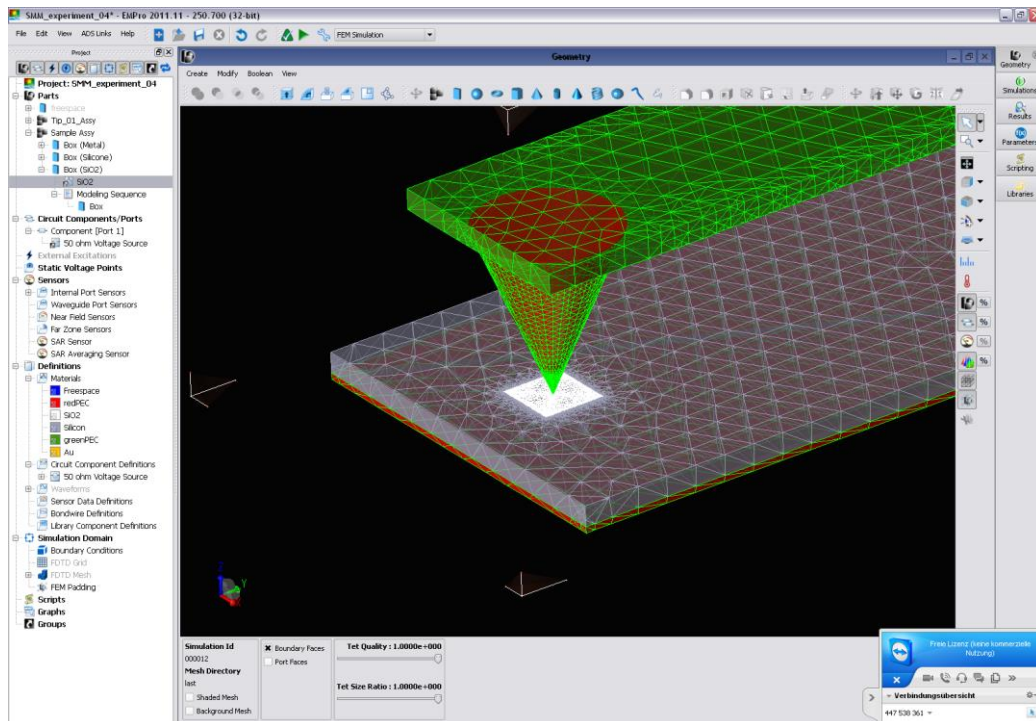
Application II: subsurface imaging application for failure analysis labs (backwafer imaging)



-> We can image from the back of the wafer and see through it

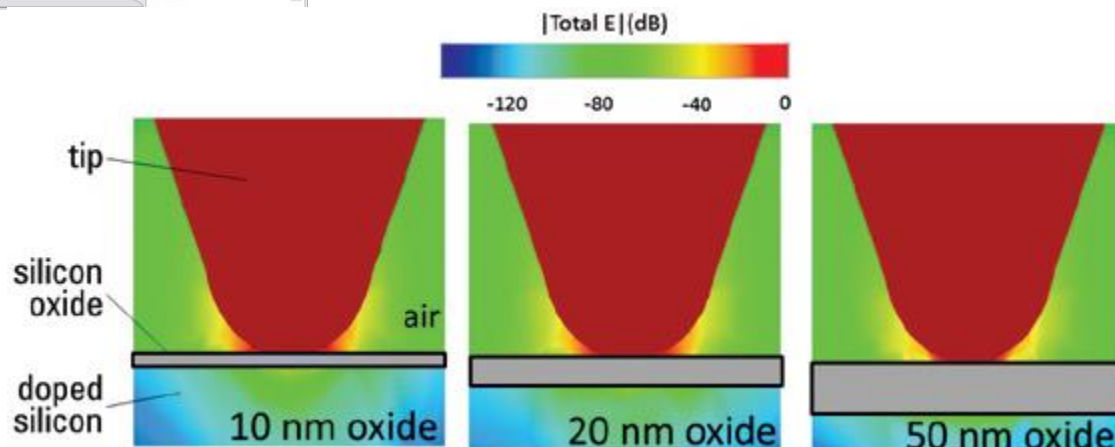


SMM project in EMPro:

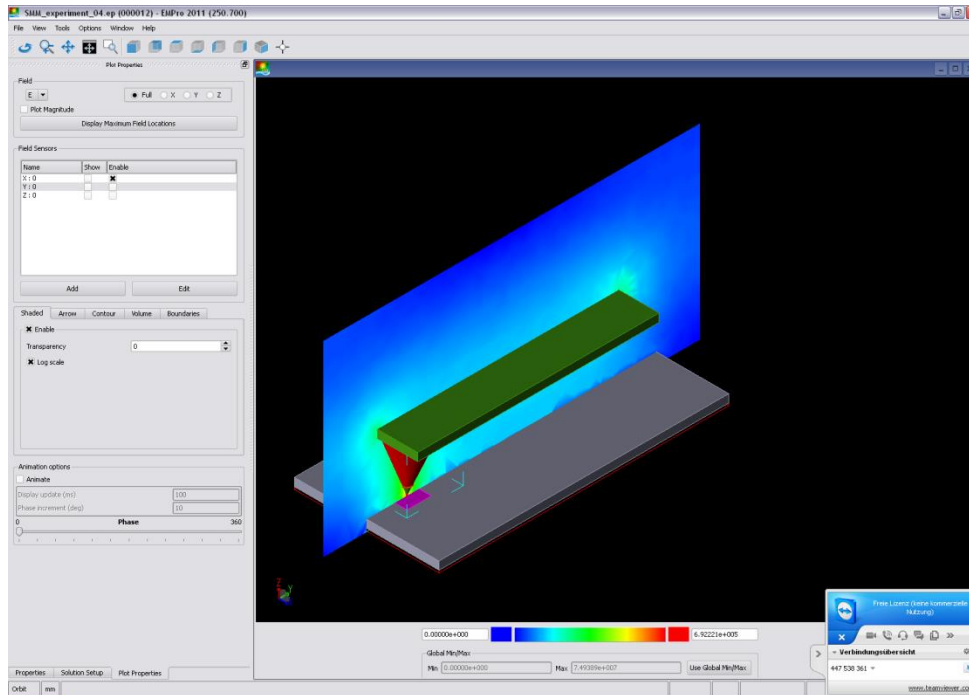


Numerical results include E-field and complex impedance

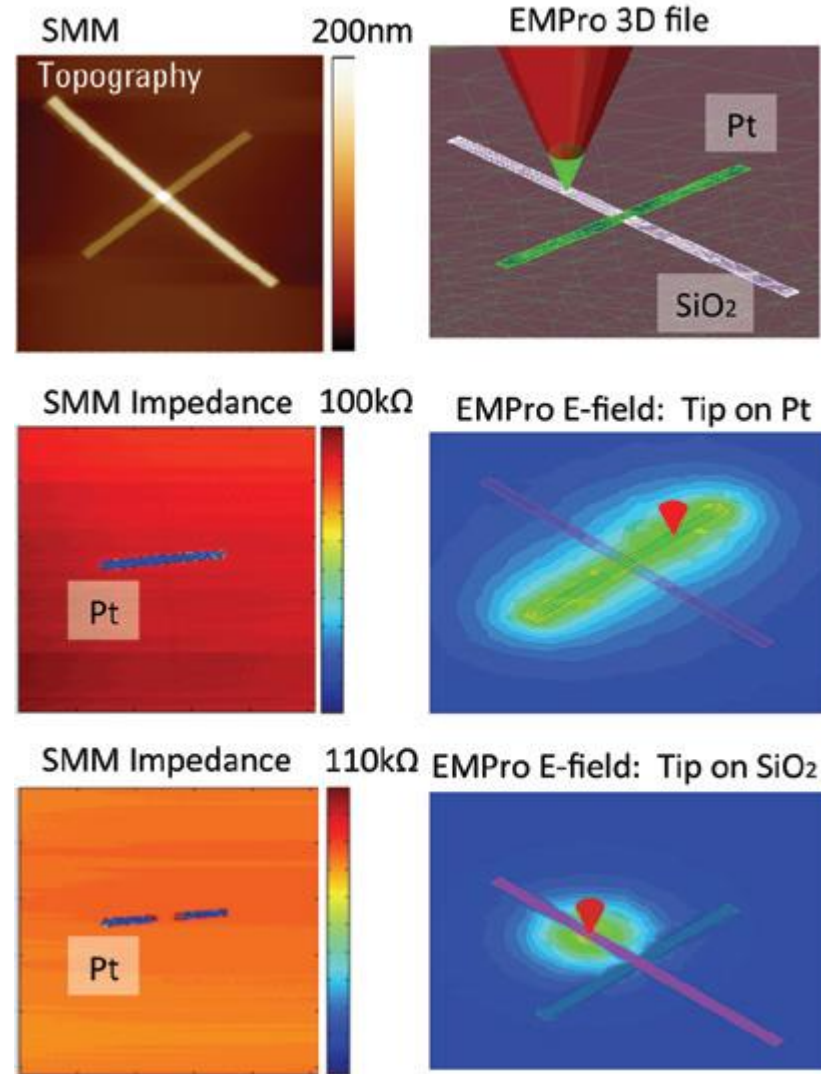
SMM project included in EMPro



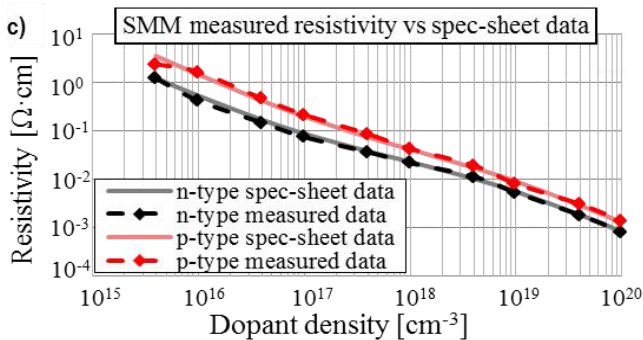
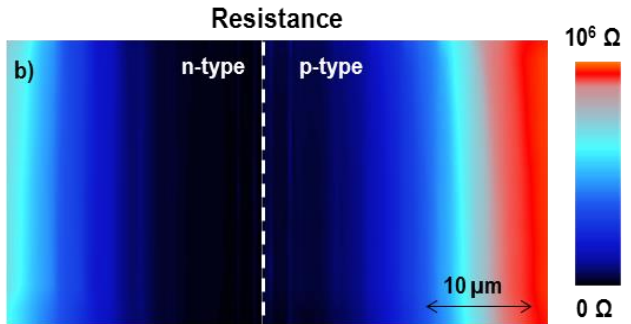
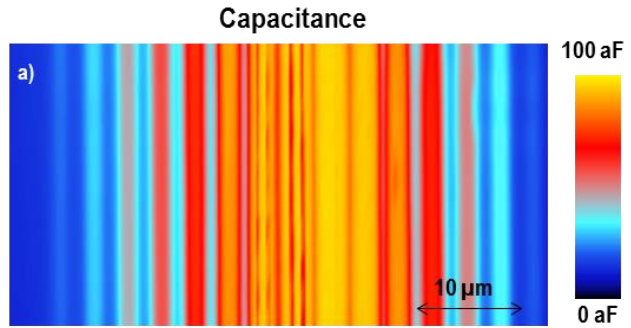
EMPro Modeling and SMM direct comparison



Kasper et al., Keysight AppNote 2013, 5991-2907
Oladipo et al., APL 103 (2013) 213106
Oladipo et al., APL 105 (2014) 133112



Application III: Resistivity from resistance



The SMM calibrated resistance R_m is converted into resistivity ρ using an analytical model:

$$R_m = \frac{\rho}{\delta} + \frac{\rho W_{DL}}{\pi r^2}$$

Where:

$$W_{DL} = \sqrt{2\epsilon\mu\rho \cdot \left(\frac{\square_{Pt} - \square_{Si} + qV_t \cdot \ln \left[\frac{N_C}{n} \right]}{q} \right)}$$

Depletion layer width

$$\delta = \left(\frac{1}{\omega} \right) \left\{ \left(\frac{\mu\epsilon}{2} \right) \left[\left(1 + \left(\frac{1}{\rho\omega\epsilon} \right)^2 \right)^{1/2} - 1 \right] \right\}^{-1/2}$$

Skin depth

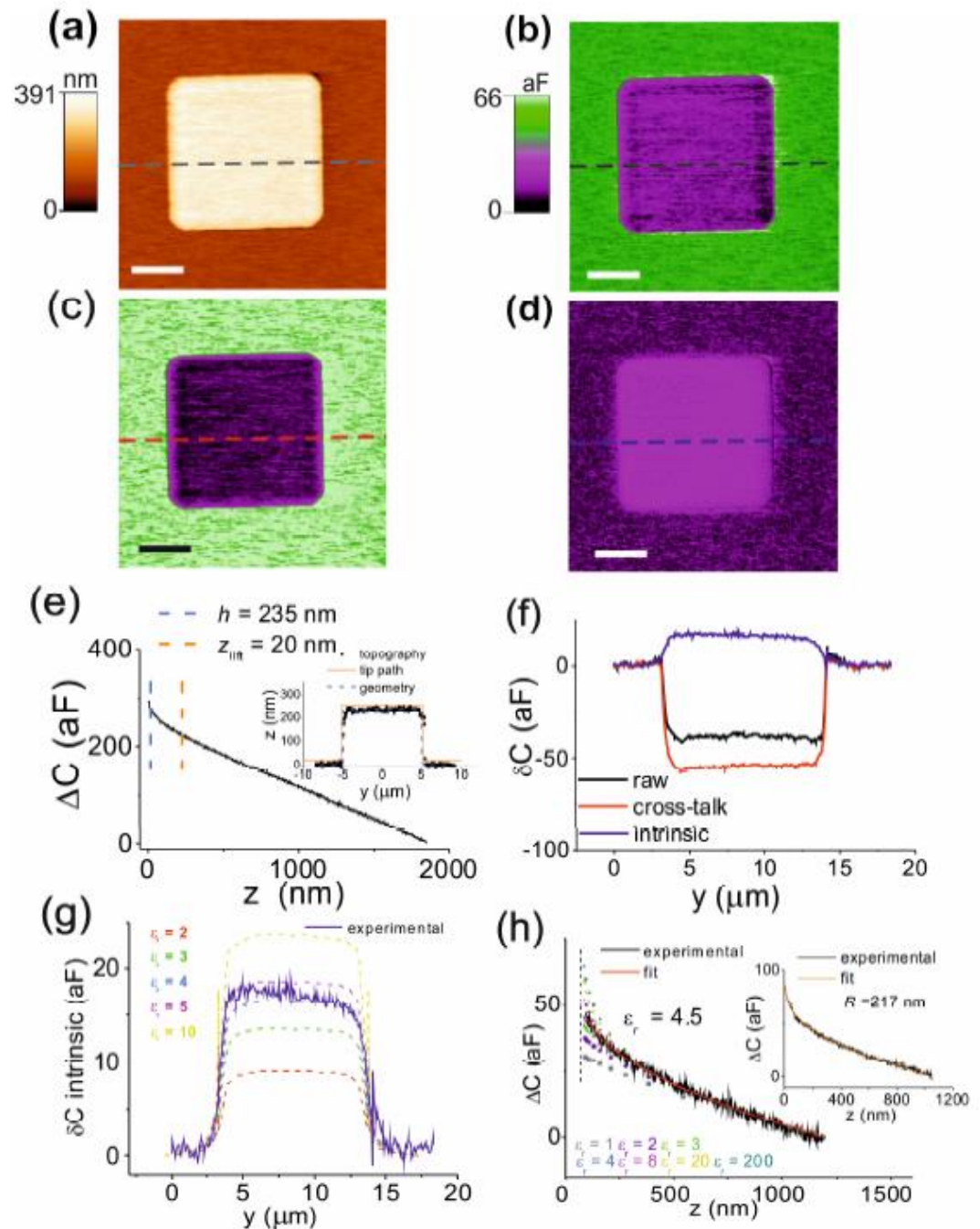
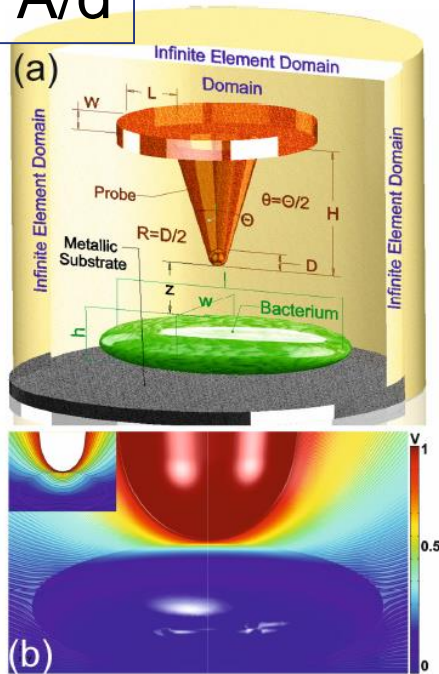
At 19GHz the depletion width ranges from 4 nm (heavily doped) to 574 nm (low doped), and the skin depth from 10 μm to 0.7 mm, respectively.

-> changing the SMM frequency modulates the values of the skin depth allowing to adjust the SMM vertical resolution for sub-surface imaging.

Brinciotti et al, Nanoscale Oct 2015

Application IV: Accurate dielectric quantification

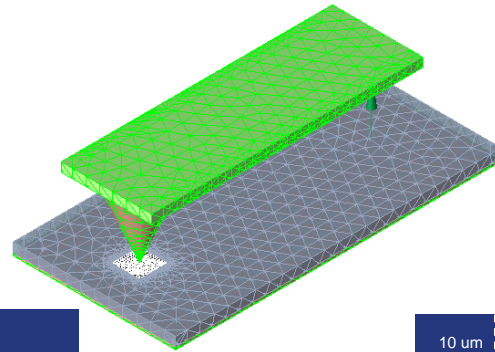
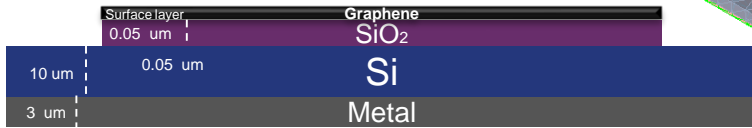
$$C = \epsilon \cdot A / d$$



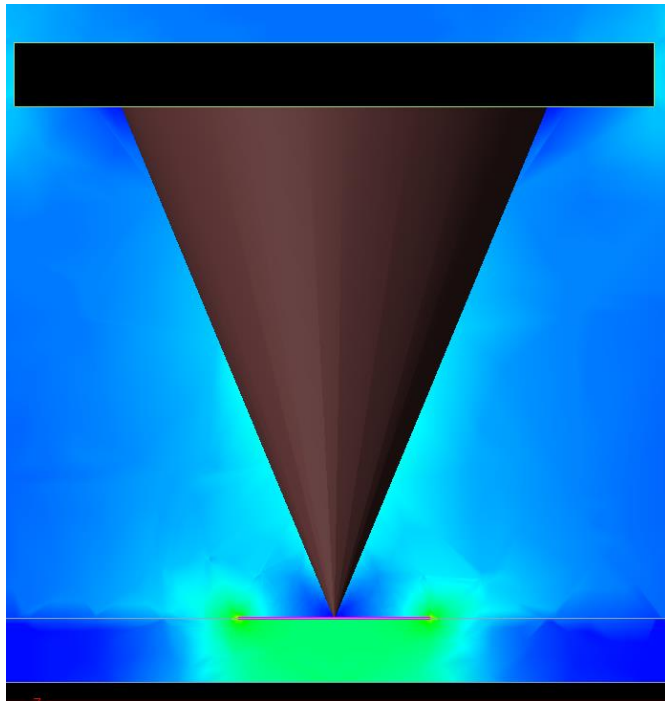
Prof. Gabriel Gomilla &
Maria-Chiara Biagi et al,
IBEC Barcelona
ACS Nano Jan 2016, 10, 280 (8p)

Application to single layer graphene:

Graphene layer included



Graphene layer not included



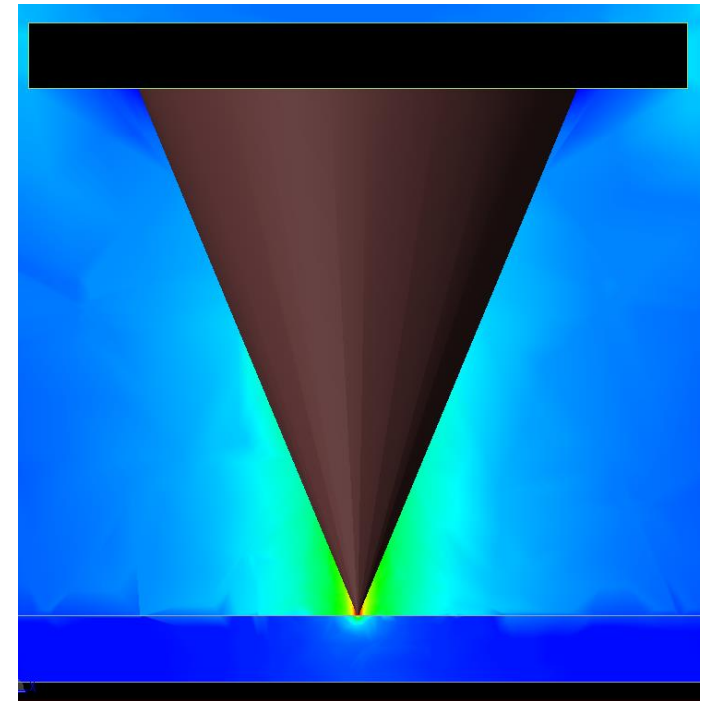
Simulated Frequency
10 GHz

Graphene model

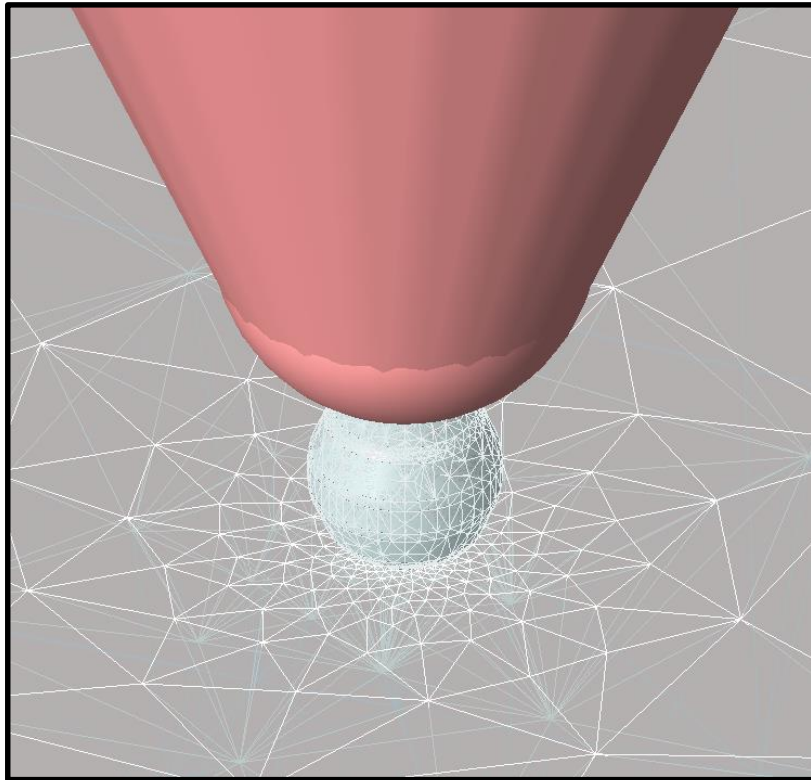
S-Parameters	-0.022 dB
Re(S11)	0.9779
Im(S11)	-0.1968
S11	0.9975
Phase(S...)	-11.381 °

Non Graphene model

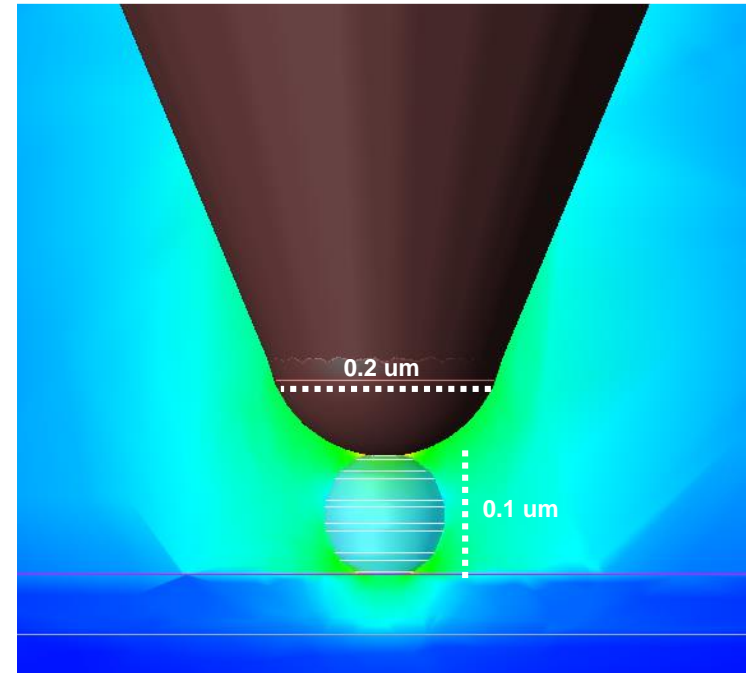
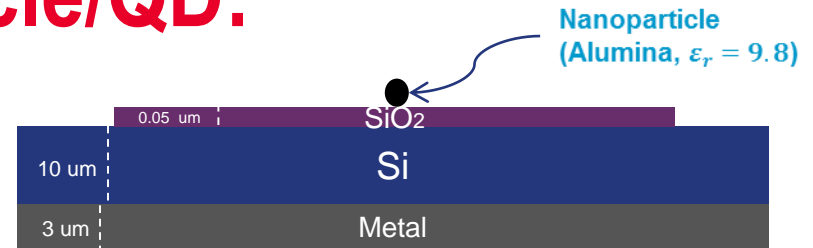
S-Parameters	-0.011 dB
Re(S11)	0.9933
Im(S11)	-0.1039
S11	0.9987
Phase(S11)	-5.969 °



Application to nanoparticle/QD:



Nanoparticle EMpro
Meshing

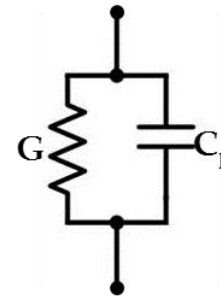
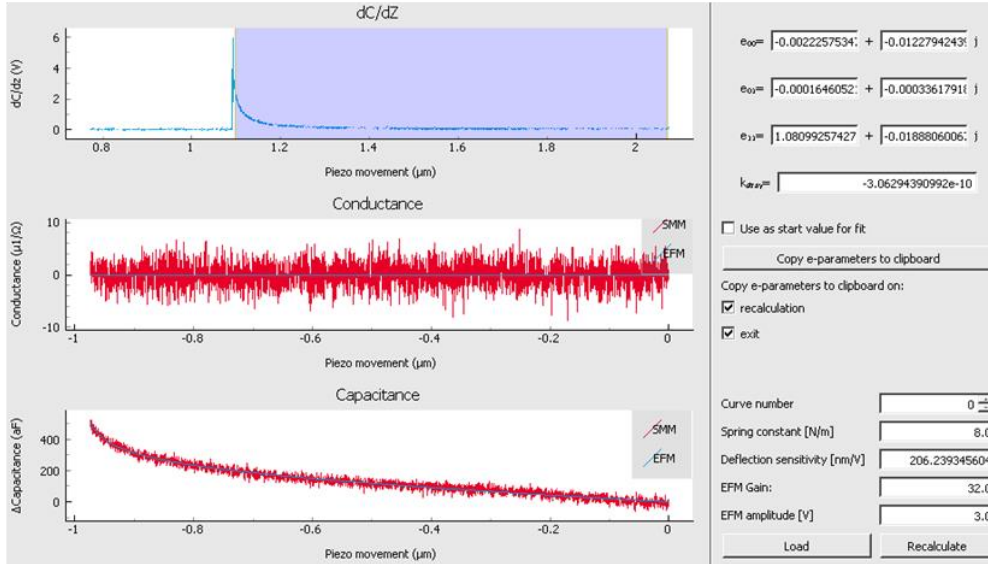


Simulated Frequency: 10 GHz

S-Parameters	-0.011 dB
Re(S11)	0.9933
Im(S11)	-0.1036
S11	0.9987
Phase(S11)	-5.955 °

Software implementation in PicoView & script:

EFM-based calibration of an EFM/SMM approach curve on Si substrate

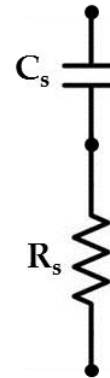


Admittance of parallel RC equivalent circuit:

$$Y = G + j*B = G + j*\omega*C_{parallel};$$

$$G = \text{Real}(Y);$$

$$C_{parallel} = \text{Imaginary}(Y) / \omega;$$



Impedance of series RC equivalent circuit:

$$Z_{series} = R_{series} + j*X = R_{series} +$$

$$1/(j*\omega*C_{series});$$

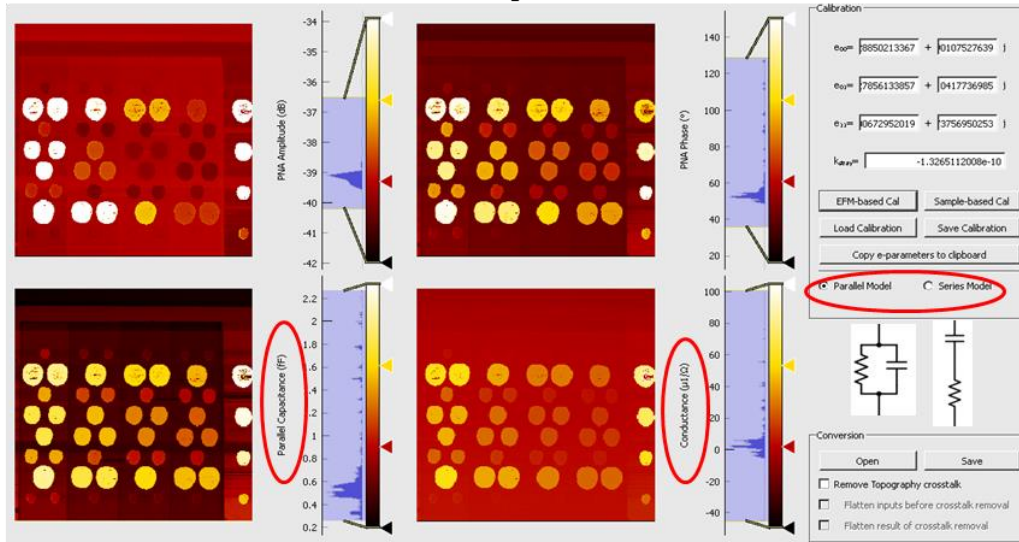
$$R_{series} = \text{Real}(Z);$$

$$C_{series} = (-1)/(\omega*\text{Imaginary}(Z));$$

$$\omega = 2*\pi*\text{frequency}; Z = 1/Y;$$

B susceptance; X reactance;

The resulted calibrated images



EFM-based calibration, described in Gramse G. et al, "Calibrated complex impedance and permittivity measurements with SMM," Nanotechnology, 2014, vol. 25, no. 14, pp. 8

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Multi-modal Keysight solutions: from products to solutions

Source meter unit SMU B2900
for advanced voltage spectroscopy



ECal unit for advanced SMM
impedance calibration in air and liquid



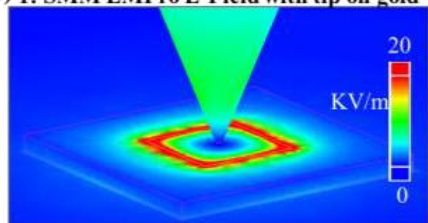
SMM



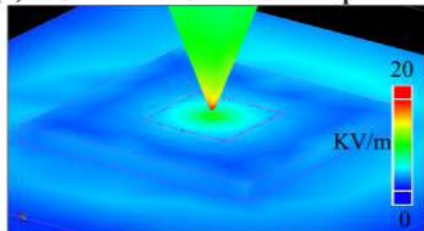
EMPro/ADS Modeling



(c) 1: SMM EMPro E-Field with tip on gold



(d) 2: SMM EMPro E-Field with tip in air



Dielectric probe kit for liquid measurements
& complex permittivity at GHz



3

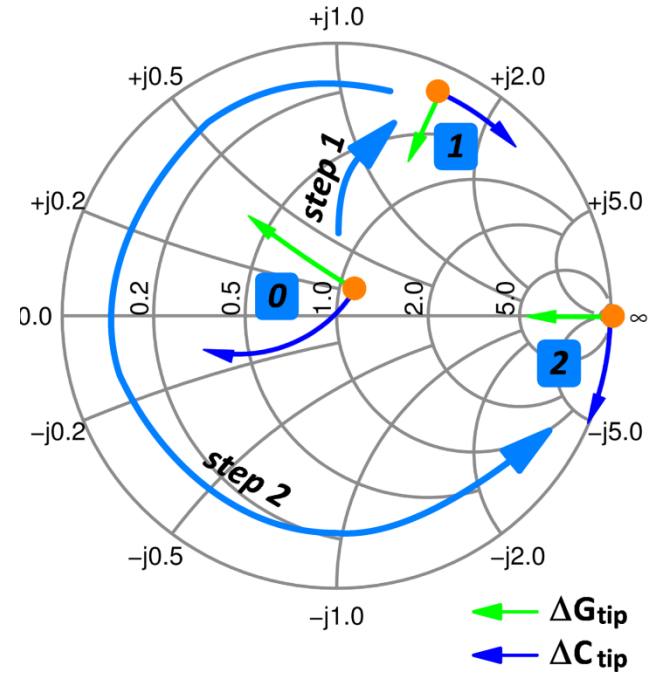
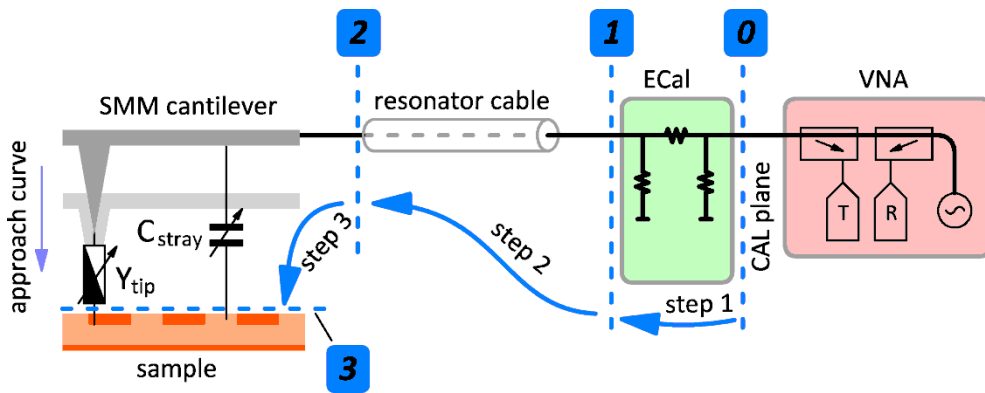
2

4

1

1. SMM+Ecal: advanced impedance calibration using time-gating, network analysis and de-embedding

Applications for advanced RF/electrical engineer labs



SMM + ECal



$$A = \frac{(1+S_{11})(1-S_{22})+S_{12}S_{21}}{2S_{21}} \quad B = Z_0 \frac{(1+S_{11})(1+S_{22})-S_{12}S_{21}}{2S_{21}}$$

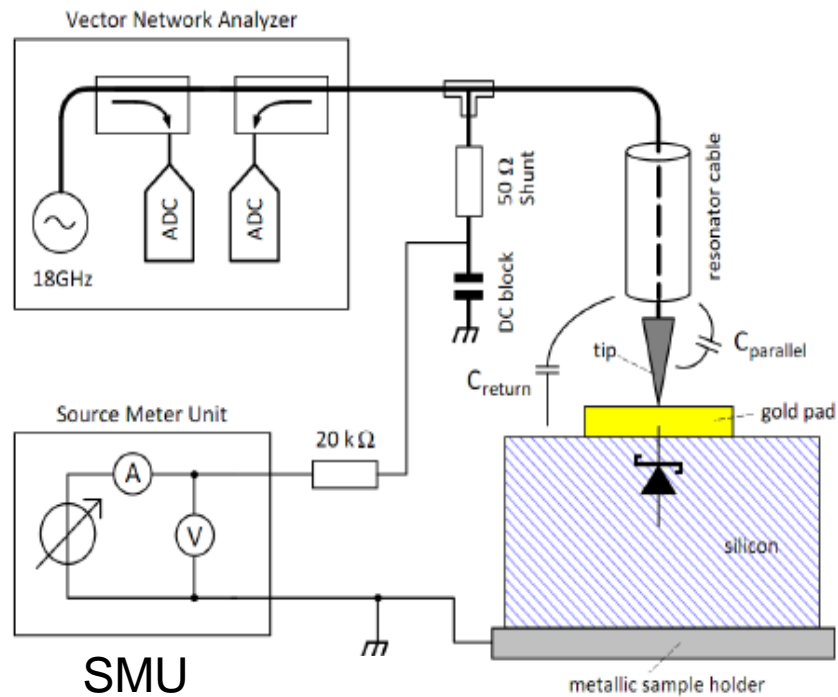
$$C = \frac{1}{Z_0} \frac{(1-S_{11})(1-S_{22})-S_{12}S_{21}}{2S_{21}} \quad D = \frac{(1-S_{11})(1+S_{22})+S_{12}S_{21}}{2S_{21}} \quad (2)$$

Kasper et al, May 2016 at IEEE IMS, San Francisco,
4 page paper conference proceeding

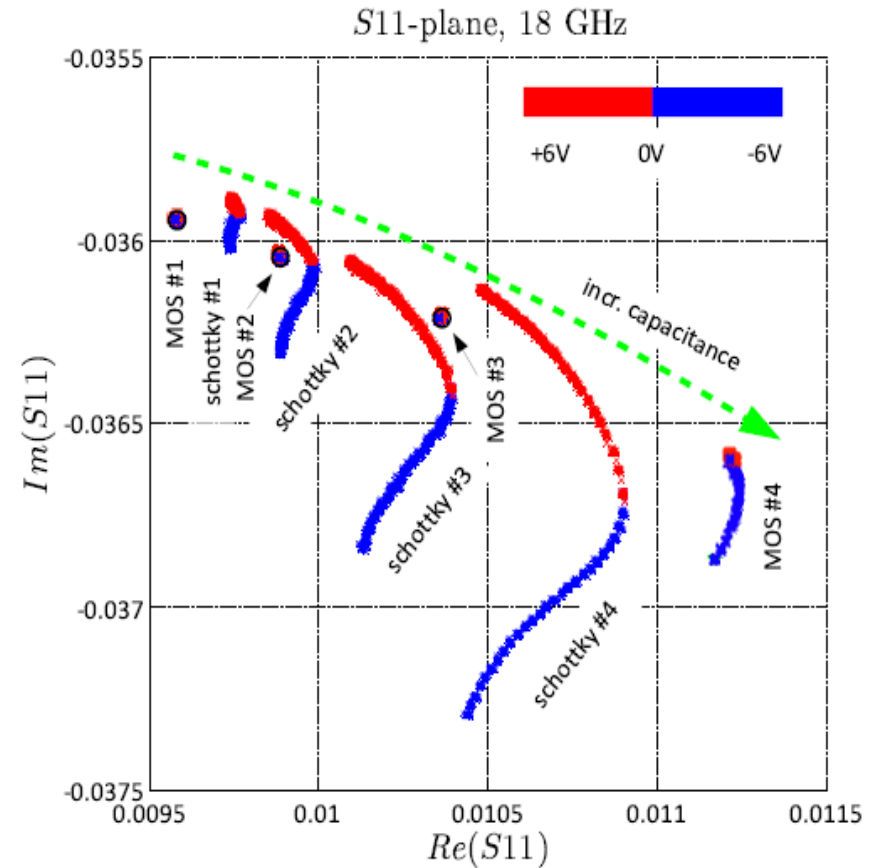
2. SMM + SMU for advanced voltage spectroscopy

Applications on electronic devices (eg MOS capacitors) and eg varactors from STMicroelectronics France

Measurement schematics (left) and SMM results (right)

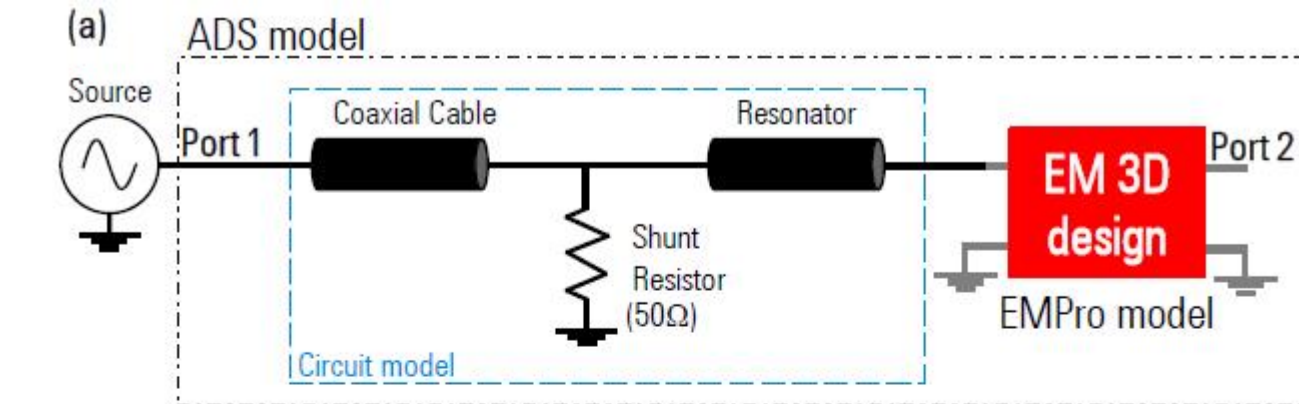


SMU

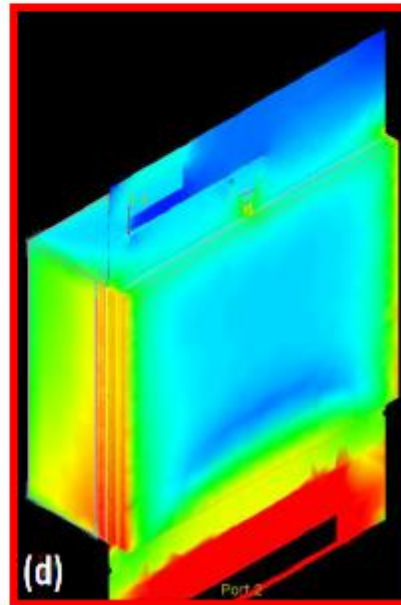
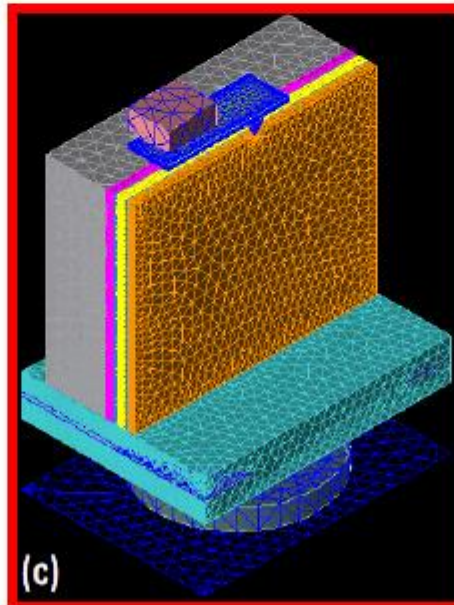
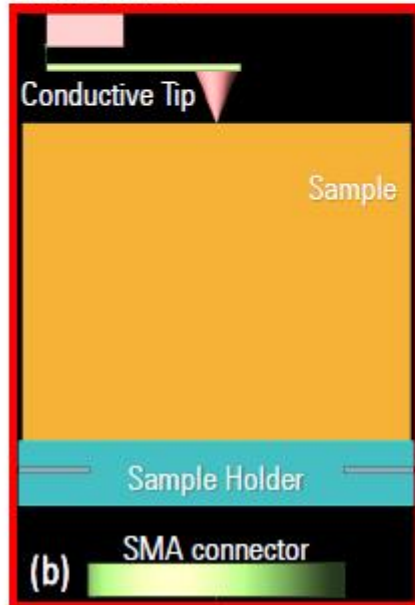


Kasper et al., JAP 2014, 116, 184301 (8 pages)

3. Transmission SMM: ADS and EMPro Modeling



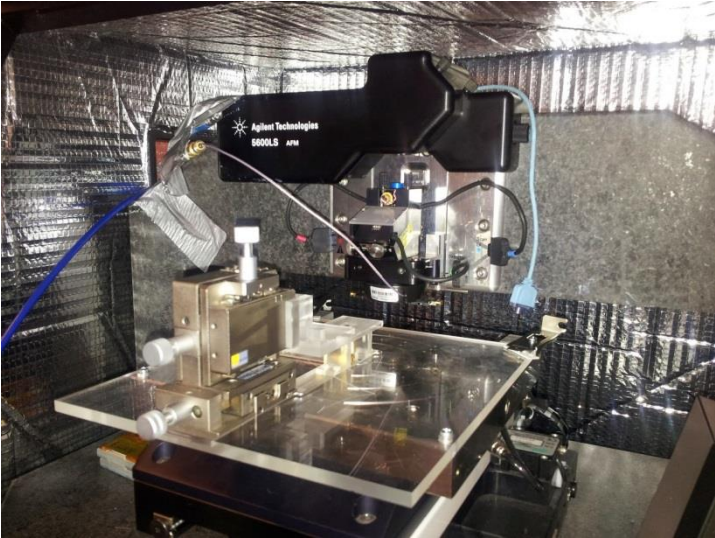
EMPro model



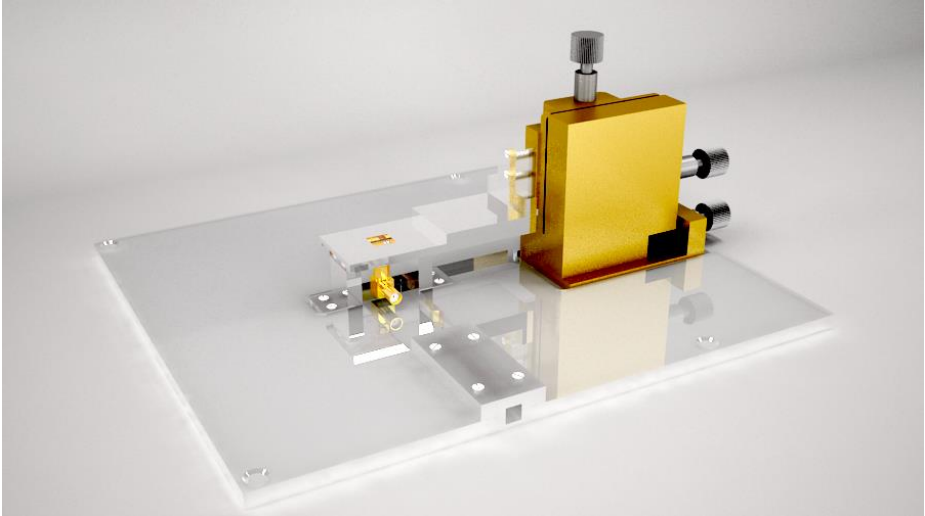
S21 transmission shown in Fernandez et al, EuMW 2015

Transmission S21 imaging: sample plate

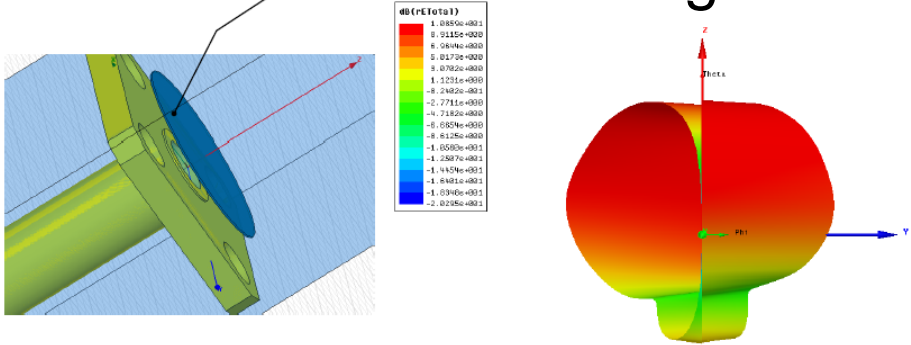
S21 sample plate integrated in 5600 SMM



Prototype sample plate CNR-IMM



E-field modeling



4. SMM for magnetic measurements

Applications for magnetic integrated circuits, MRAM's, ferromagnetic resonance FMR, and multi-ferroic samples

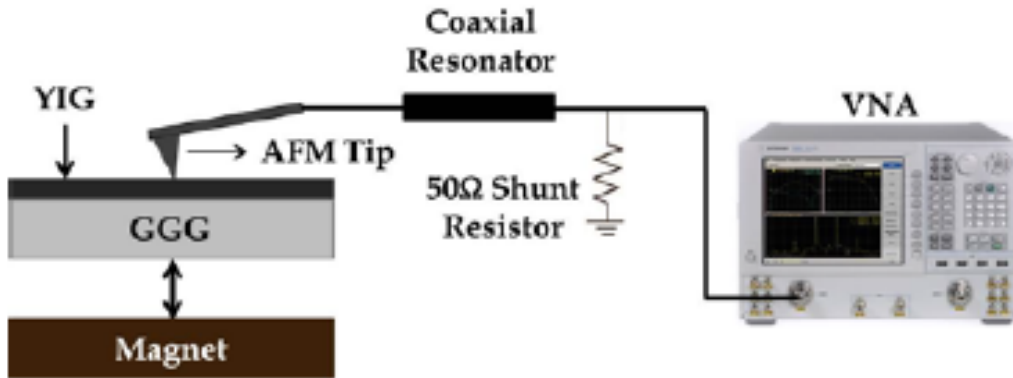


Fig. 1. Schematic of the experimental setup

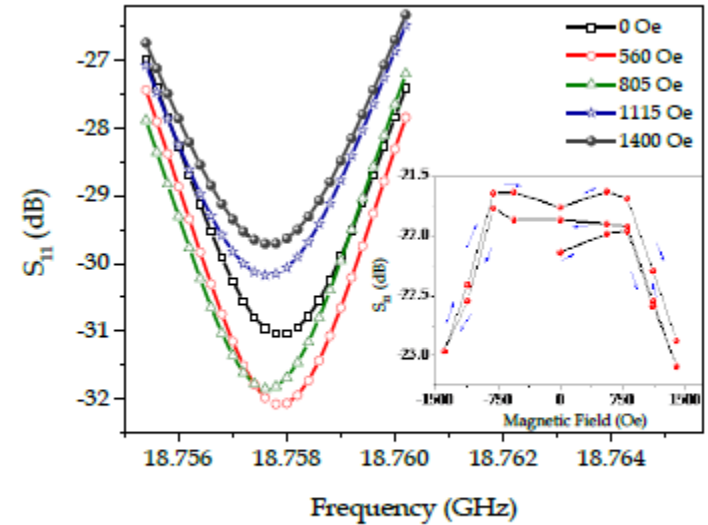


Fig. 3. The measured S_{11} for the RF sputtered YIG with respect to different external magnetic fields. Inset shows the hysteresis behavior of the sample.

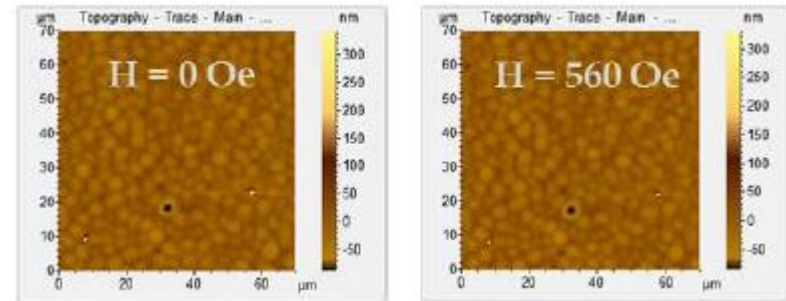
$$S_{11} = \frac{Z_{total} - Z_0}{Z_{total} + Z_0} \quad (1)$$

$Z_{total} = Z_{Resonator} + Z_{Sample}$. Here, $Z_{Resonator}$ is the impedance of the $\lambda/2$ coaxial line resonator. Z_{Sample} is a bi-layer system with YIG film and GGG substrate, defined as:

$$Z_{Sample} = Z_{YIG} \frac{Z_{GGG} + iZ_{YIG} \tan(k_{YIG} t_{YIG})}{Z_{YIG} + iZ_{GGG} \tan(k_{YIG} t_{YIG})} \quad (2)$$

Magnetic EMPro modeling results

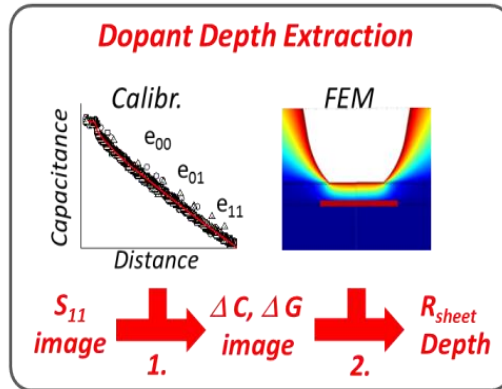
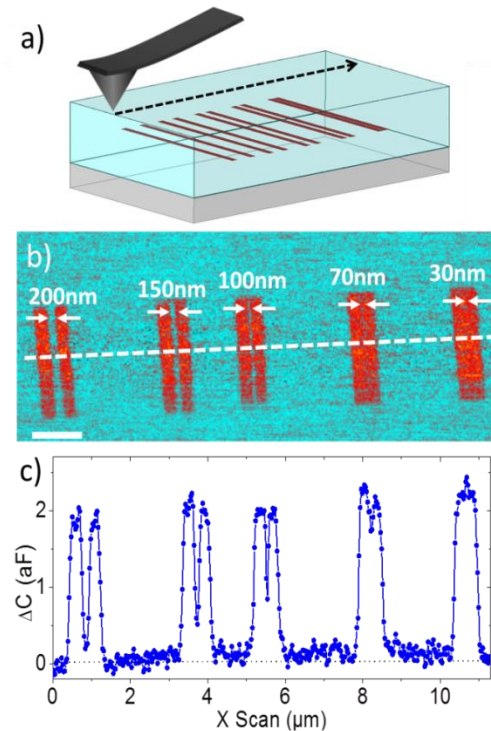
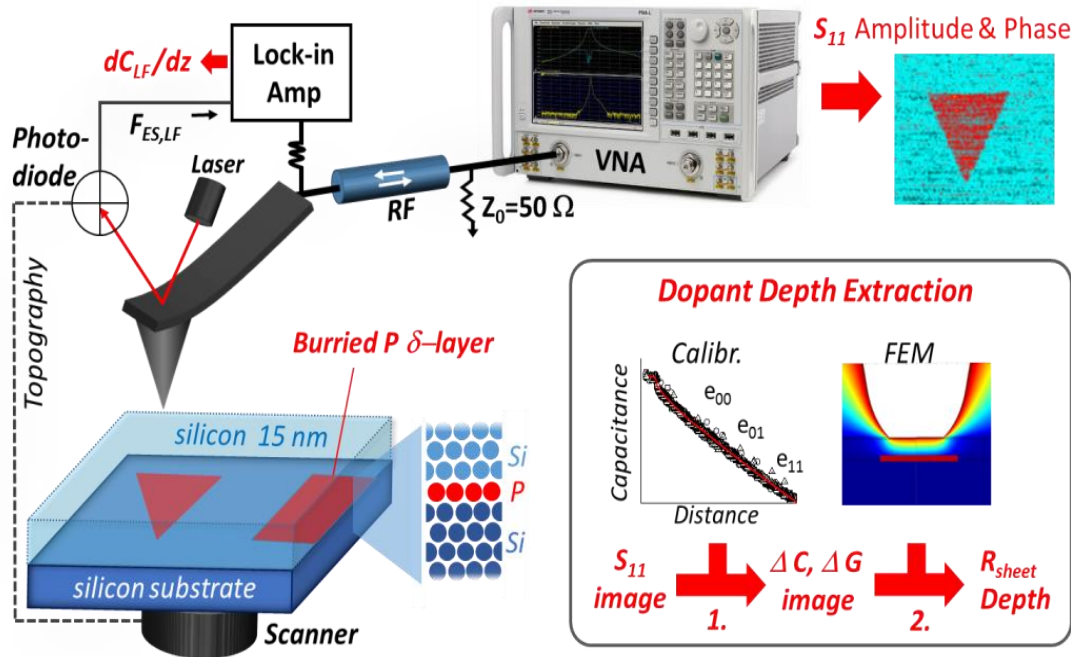
μ_r	$Z_{sample} (\Omega)$	Conductance (fS)	Capacitance (aF)
1.0001711+j*0.9998	1.246-j*1308812.375	727.38	12.16



5. SMM for quantum electronic Qubits

Research collaboration with UC London (Prof Neil Curson) and London quantum technology hub

SMM for silicon QuBits



- Characterizing buried nanostructures and electrical properties of atomic thick delta dopant layers used for quantum processes.
- Talk at silicon quantum electronic workshop in June 2016.
- Gramse et al, 2018

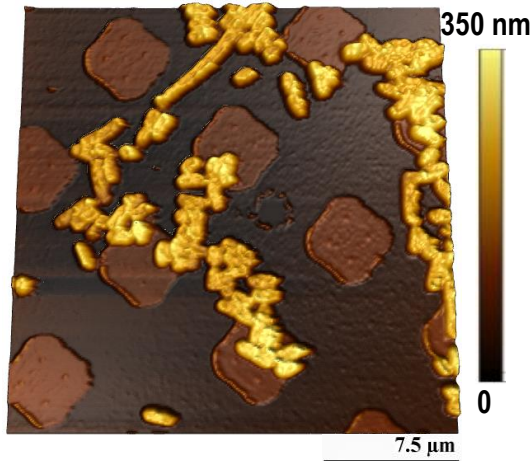
Agenda

- Overview & SMM Introduction
- Dopant profiling (dC/dV) for semiconductors
- Complex impedance for materials science
 - Calibration
 - Subsurface imaging
 - Resistivity from resistance
 - Dielectric quantification
 - 2D materials (graphene)
- Multi-modal SMM solutions
 - Augmented SMM (SMM plus add-ons)
 - New modes: transmission, magnetic, and QuBits
- **Bio-SMM & liquid imaging**
- Summary

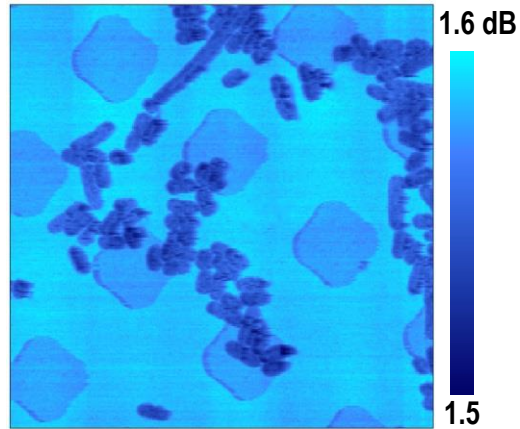
7500 Bio-SMM in air: E. Coli bacteria over highly doped Si with SiO₂ pillars

Tapping AAC mode

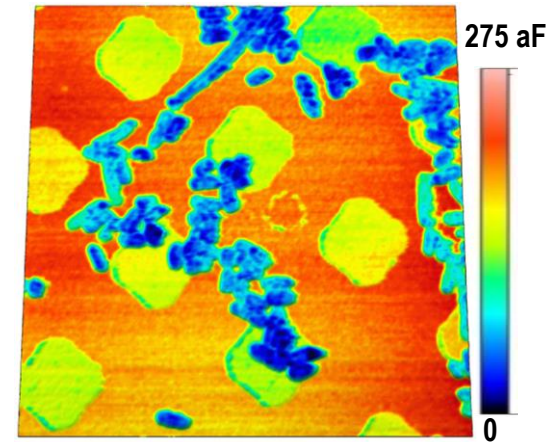
Topography



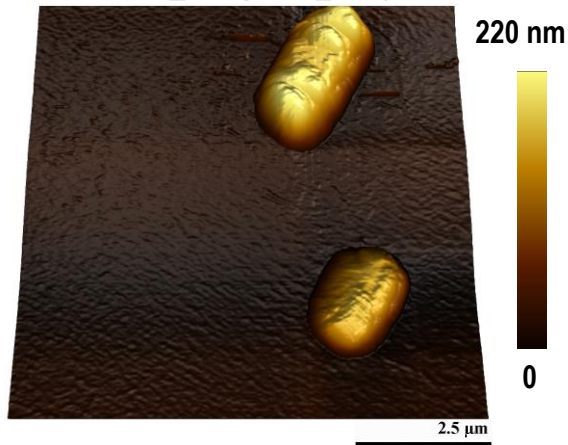
Microwave Amplitude



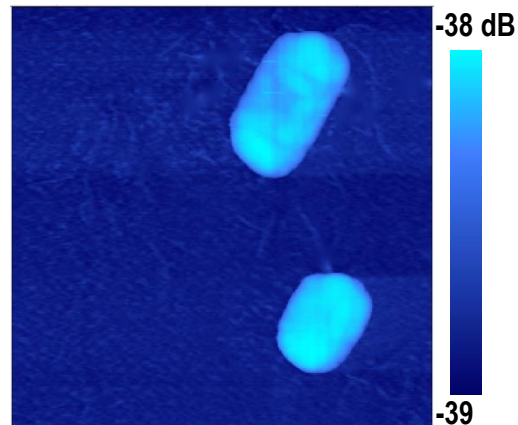
Capacitance



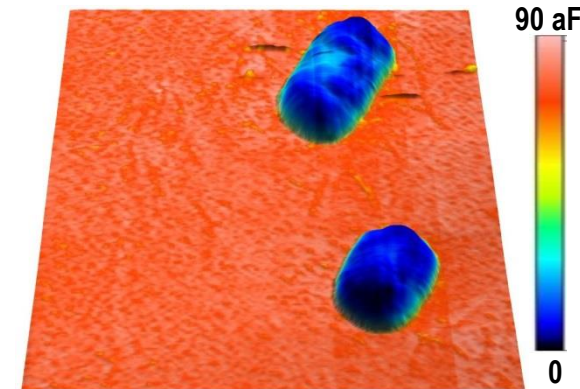
Topography



Microwave Amplitude



Capacitance



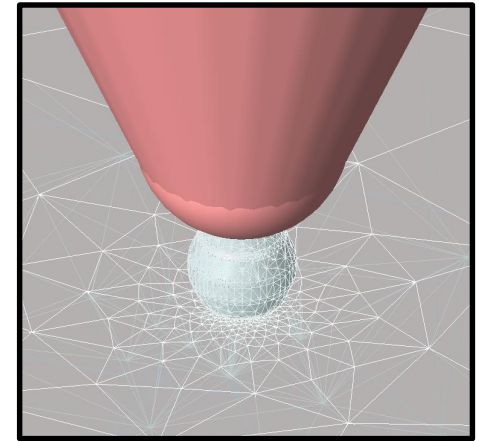
CHO cells in humid air (f=20 GHz)

Single *E-coli* bacteria imaged at 20 GHz frequency using the scanning microwave microscope (SMM)

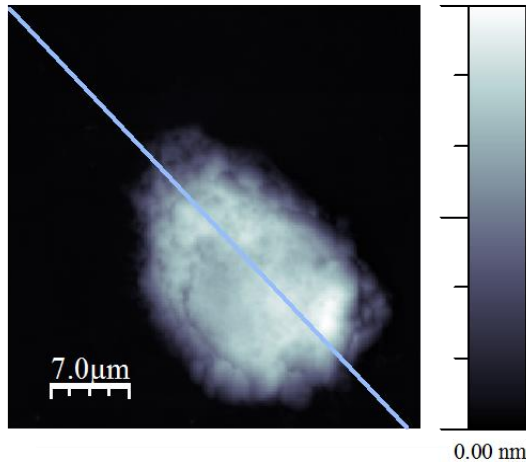
Silviu-Sorin Tuca¹, Georg Gramse¹, Manuel Kasper², Enrico Brinciotti², Yoo-Jin Oh¹, Giulio Maria Campagnaro², Giorgio Badino², Peter Hinterdorfer¹, Ferry Kienberger²

¹ Johannes Kepler University of Linz, Institute of Biophysics, Gruberstrasse 40, A-4020, Linz, Austria
² Keysight Technologies Austria GmbH, Measurement Research Lab, Gruberstrasse 40, A-4020, Linz, Austria

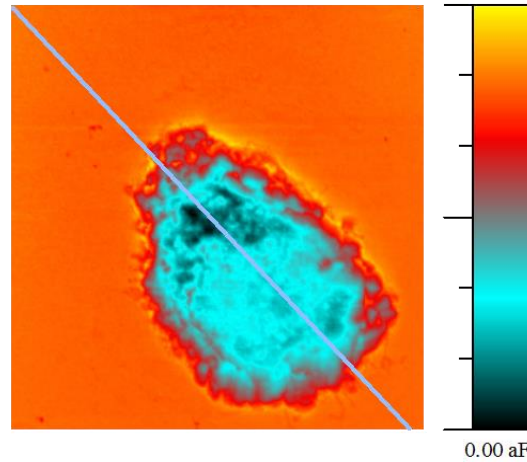
EMPro of tip-sample mashing



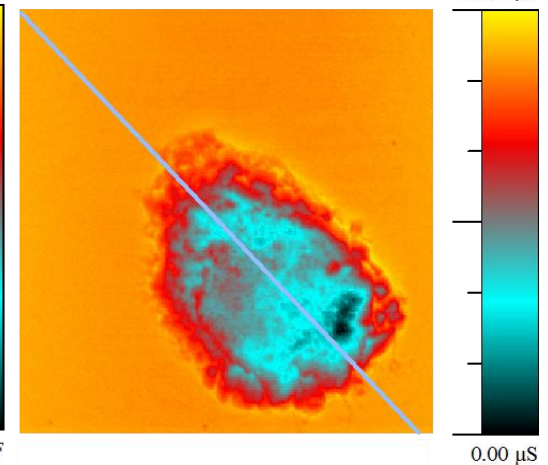
Topography



Capacitance

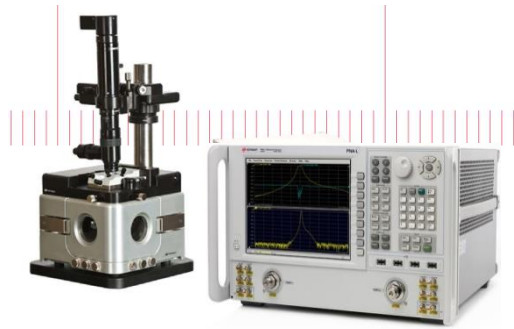


Conductance

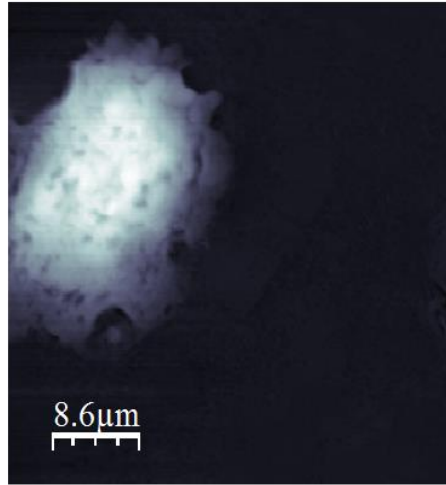


Contact & tapping mode

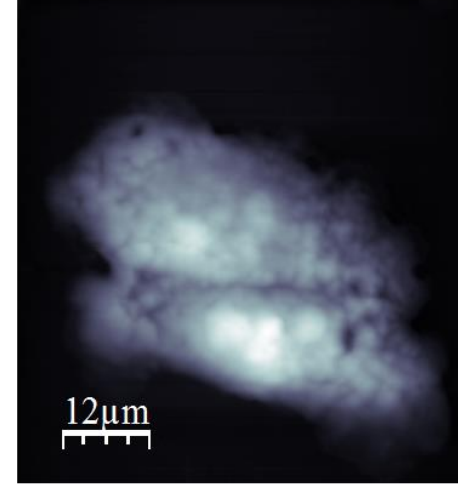
Bio-measurements in liquid using the 7500 SMM



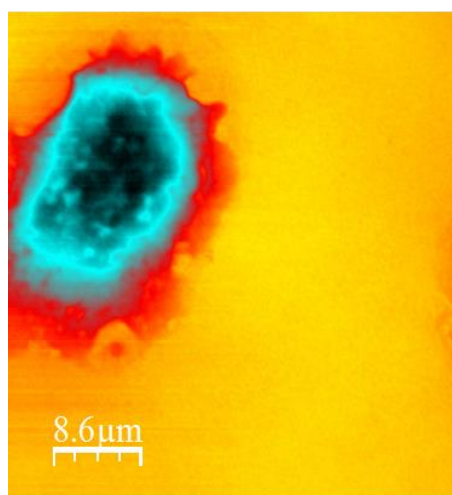
Topography



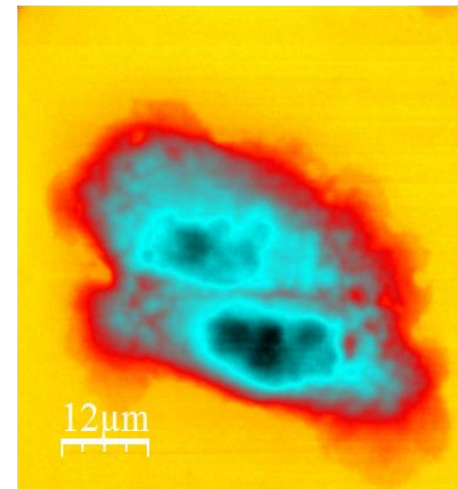
Topography



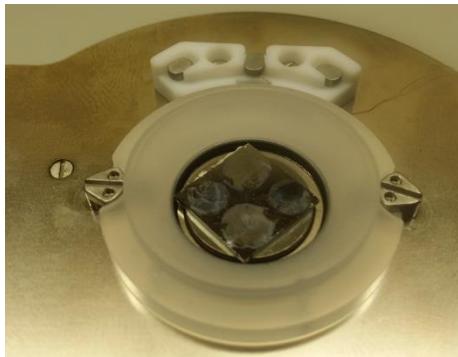
PNA Phase



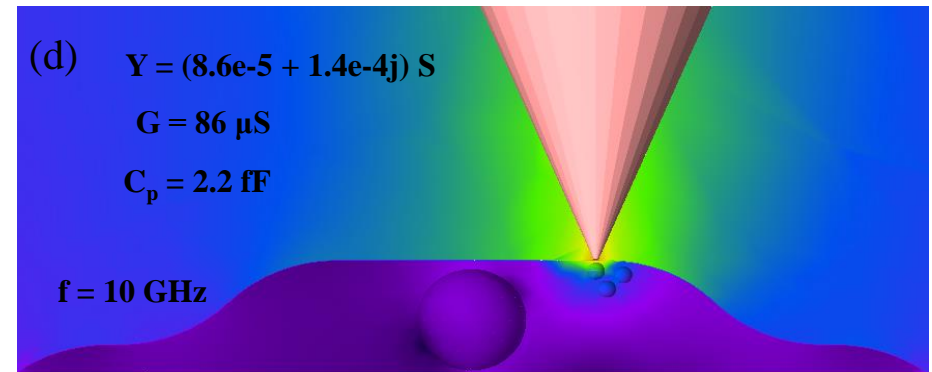
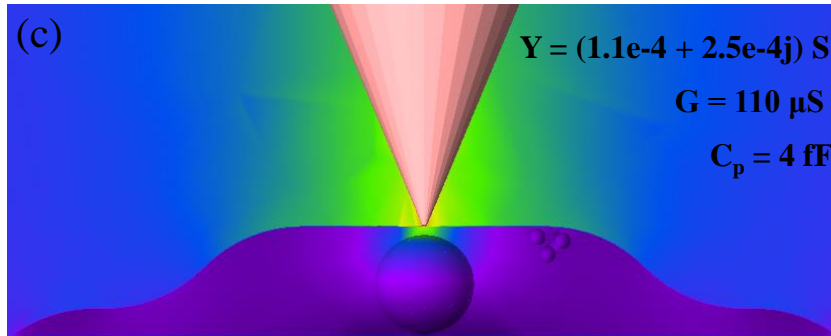
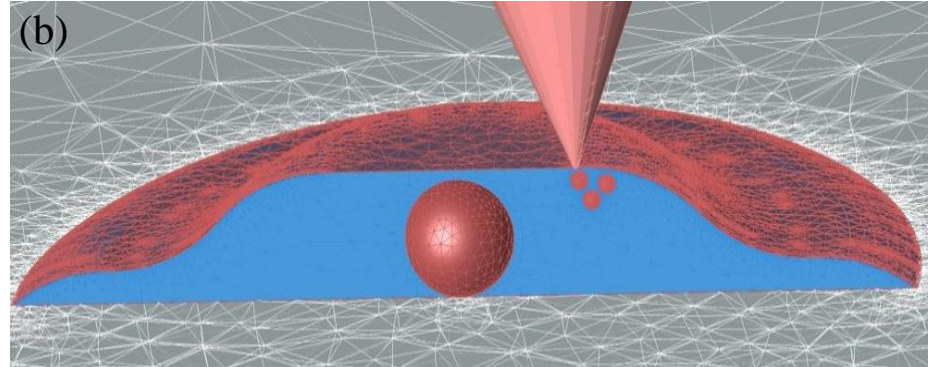
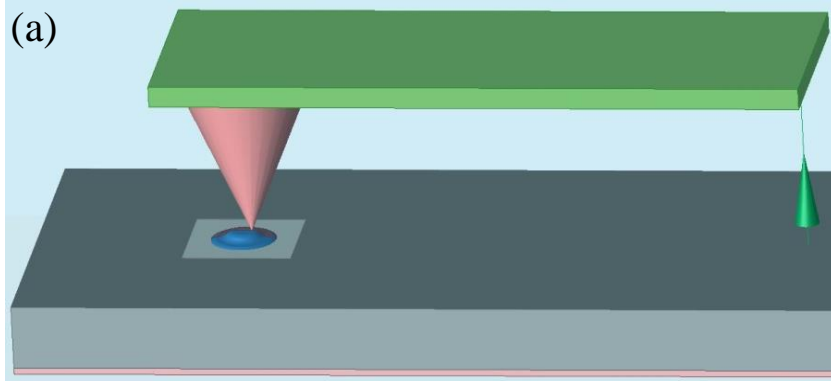
PNA Phase



N9721B Liquid cell:



Application to cells in liquid: meshing, E-fields and complex impedance values

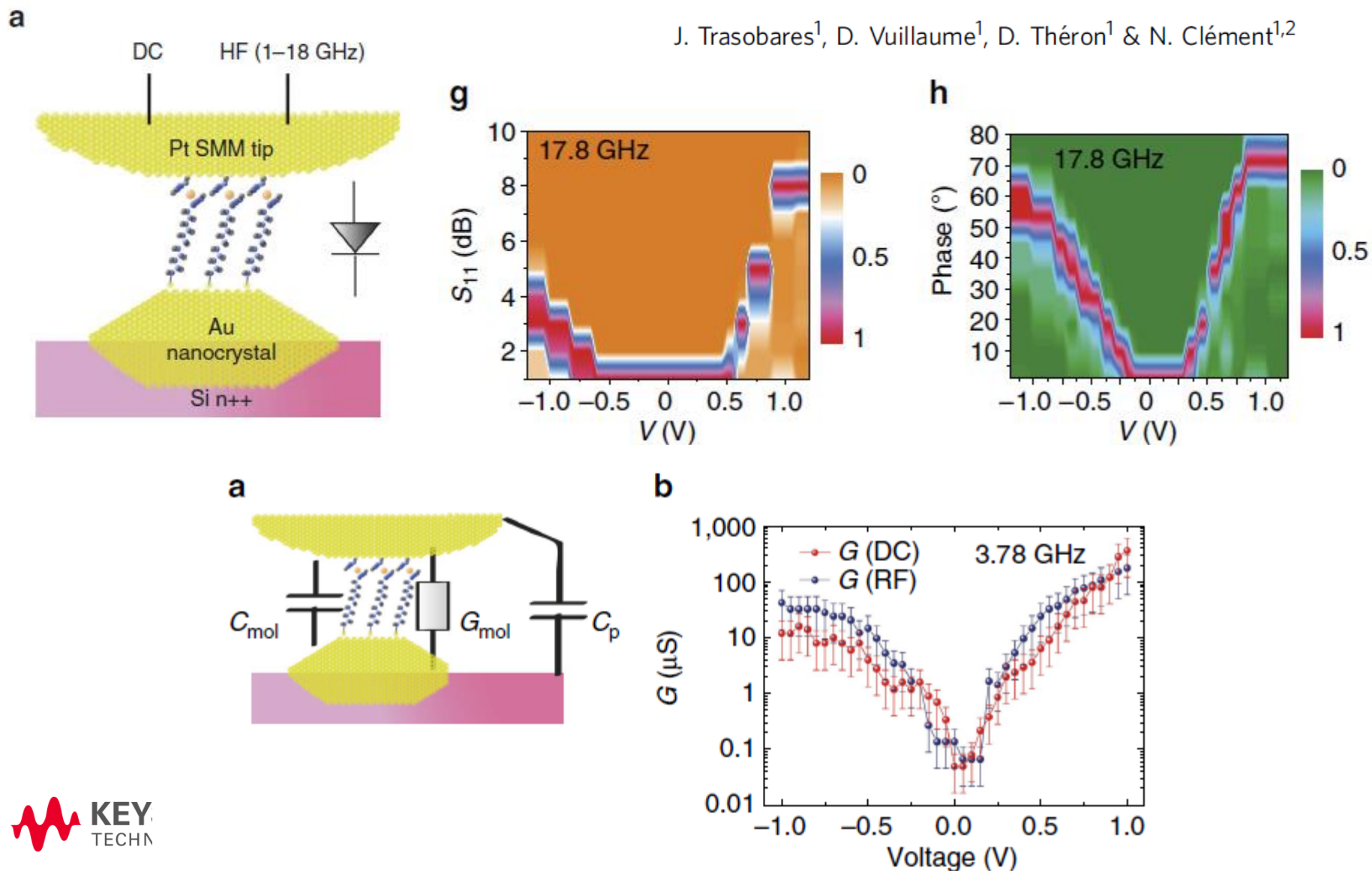


|Total E|: (dB) Reference value: $3e+7 V/m$



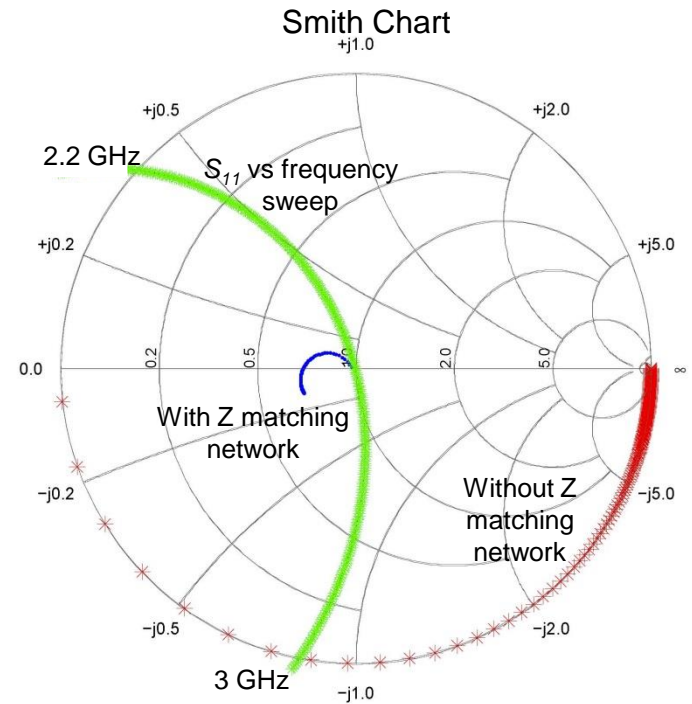
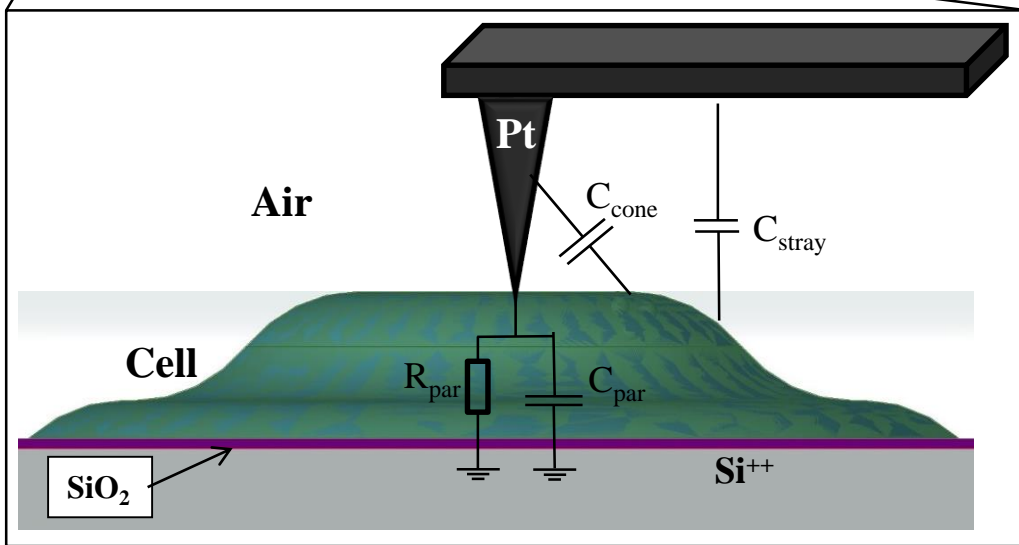
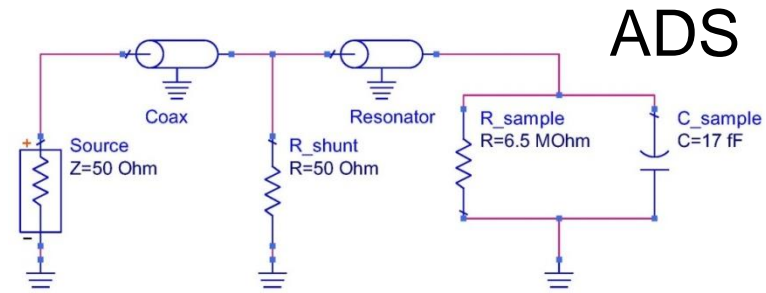
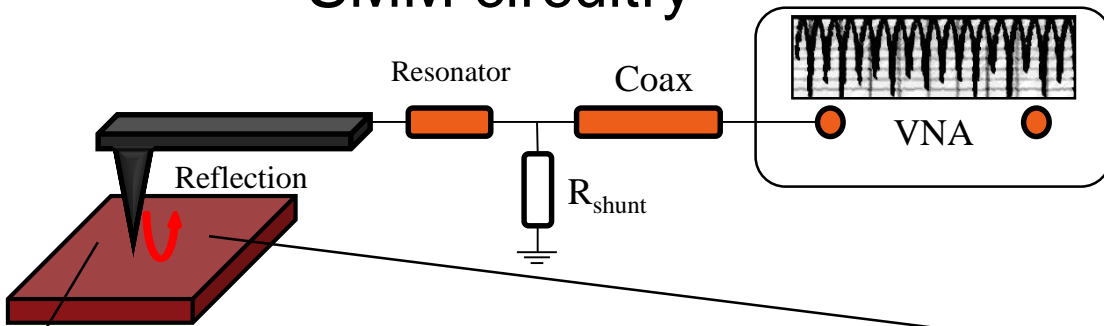
A 17 GHz molecular rectifier

J. Trasobares¹, D. Vuillaume¹, D. Théron¹ & N. Clément^{1,2}



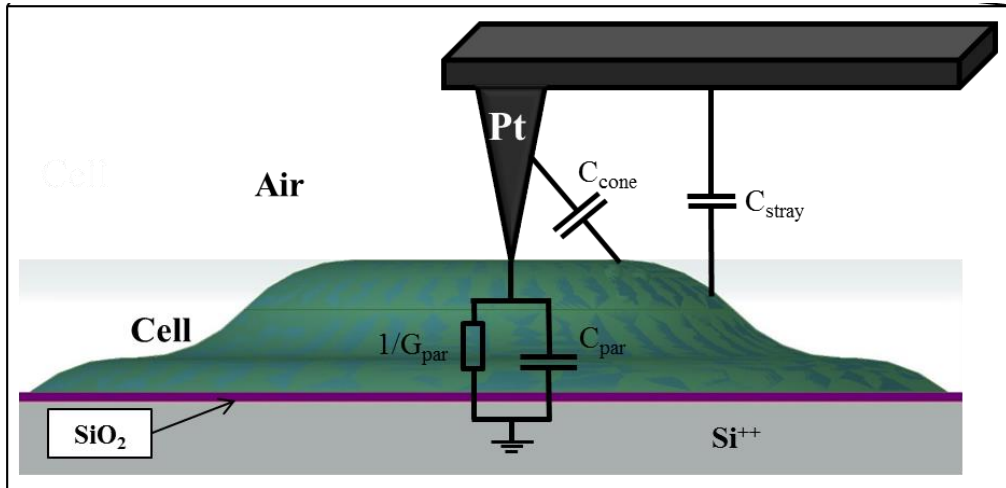
Data interpretation using ADS Smith chart analysis and EMPro modeling

SMM circuitry

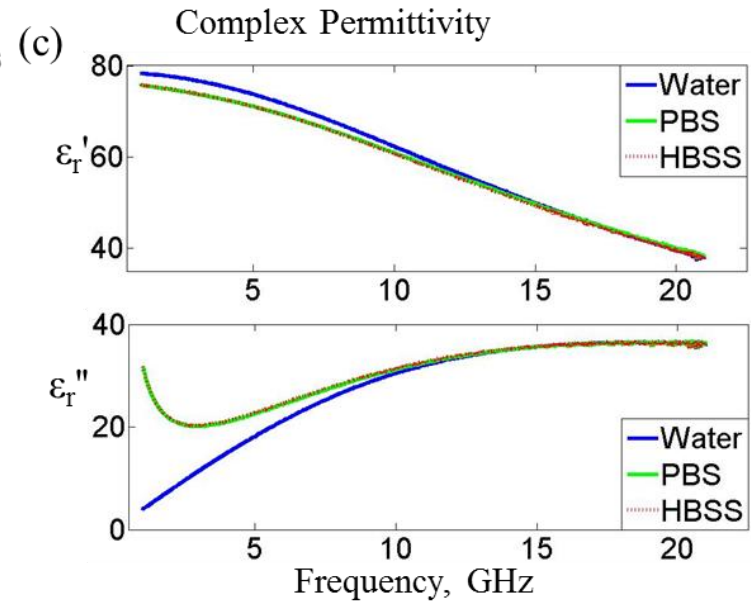
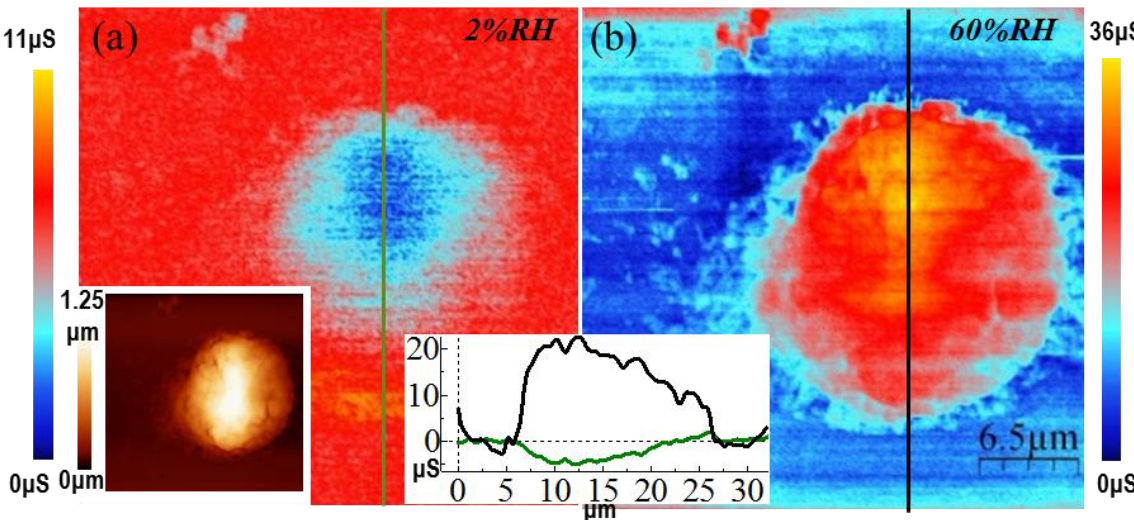


Tuca et al, Nanotechnology 2016, 27, 135702 (9p)

3. SMM + dielectric probe kit for complex permittivity



CHO Conductance with varying humidity



Agenda

- Overview & SMM Introduction
- Dopant profiling (dC/dV) for semiconductors
- Complex impedance for materials science
 - Calibration
 - Subsurface imaging
 - Resistivity from resistance
 - Dielectric quantification
 - 2D materials (graphene)
- Multi-modal SMM solutions
 - Augmented SMM (SMM plus add-ons)
 - New modes: transmission, magnetic, and QuBits
- Bio-SMM & liquid imaging
- **Summary**

Summary general:

Ability to do **broadband** measurements, at frequencies from **1 GHz up to 20 GHz**,

- of **calibrated complex impedance** in materials science,
- of **calibrated dopant profiles** in semicon,
- of **C-V curve** spectra,
- of cells and electrochemistry in **liquid**,

and to compare the data from all these measurements with **semiquantitative 3D models** implemented in EMPro.

For all of this we **offer integrated** solutions based on several of our products: PNA-AFM, SMU, Ecal, dielectric probe kit, EMPro/ADS, ...

Various **workflows** have been implemented showing different **use cases**.

Summary details:

Differentiators

- Calibrated complex impedance
 - Capacitance and resistance: 0.5 aF sensitivity, differences of 20 Ohm can be measured up to 20 kOhm
- ***Materials properties can be determined:***
 - ***From capacitance the complex permittivity/dielectric constant (~10% accuracy)***
 - ***From resistance the resistivity (aka SSRM)***
- Calibrated dopant density for both silicon and compound semiconductors, as well as other electronic materials, large dynamic range for dopant density
- All info in one scan (topo, impedance, dopant) with high spatial resolution: ~ 10 nm
- ***Broadband frequencies (1-20 GHz) allowing for variable depth subsurface imaging and frequency selective dopant profiling***
- ***The 7500 bio-SMM works in liquid***
- Technology synergy with other Keysight products: EMPro; source-meter unit SMU; Ecal calibration unit; dielectric probe kit for permittivity

Thanks for your interest and
your attention.

ferry_kienberger@keysight.com